







NAVAL POSTGRADUATE SCHOOL Monterey, California



THESIS

NATURAL CONVECTION COOLING OF A 3 BY 3
ARRAY OF RECTANGULAR PROTRUSIONS IN AN
ENCLOSURE FILLED WITH DIELECTRIC LIQUID:
EFFECTS OF BOUNDARY CONDITIONS
AND COMPONENT ORIENTATION

by

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December 1988

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		REPORT DOCUM	ENTATION PAGE		
a Report Security Classification Unclassified			1b Restrictive Markings		
a Security Classification Authori	ty		3 Distribution Availability of Report		
b Declassification/Downgrading	Schedule		Approved for public release; distribu	ation is unlimited.	
Performing Organization Repor		r(s)	5 Monitoring Organization Report Number(s)	
a Name of Performing Organizat		6b Office Symbol	7a Name of Monitoring Organization		
Naval Postgraduate School		(If Applicable)	Naval Postgraduate School		
c Address (city, state, and ZIP co	ide)		7b Address (city, state, and ZIP code)		
Monterey, CA 93943-5000		1	Monterey, CA 93943-5000		
a Name of Funding/Sponsoring Organ		8b Office Symbol (If Applicable)	9 Procurement Instrument Identification Number		
c Address (city, state, and ZIP co	ode)		10 Source of Funding Numbers		
		10	Program Element Number Project No Task No Work Unit Accession No		
			oling of a 3 by 3 Array of Rectangular		
			ary Conditions and Component Orient	ation	
2 Personal Author(s) Edgardo					
3a Type of Report 13b Master's Thesis Fro	Time C	overed To	14 Date of Report (year, month,day) December 1988	15 Page Count 139	
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Distribution/Availability of A X unclassified/unlimited	same as r	eport DTIC users	21 Abstract Security Classification Unclassified 22b Telephone (Include Area code) (408) 646-3400	22c Office Symbol	
DD FORM 1473, 84 MAR		83 APR edition may		classification of this page	
		All other edition	ons are obsolete	Unclassified	

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Natural Convection Cooling of a 3 by 3 Array of Rectangular Protrusions in an Enclosure Filled with Dielectric Liquid: Effects of Boundary Conditions and Component Orientation

by

Edgardo I. Torres LT, Columbian Navy B.S., Columbian Naval Academy, 1986

Submitted in partial fulfillment of the requirements for the degree of

MASTER OF SCIENCE IN MECHANICAL ENGINEERING

from the

NAVAL POSTGRADUATE SCHOOL December 1988

ABSTRACT

An experimental investigation of natural convection immersion cooling of two configurations of discrete heat sources in an enclosure filled with Fluorinert FC-75 has been conducted. A three by three array of rectangular protrusions was employed.

In the first study, using the same equipment set-up of Benedict [Ref. 13], the influence of changing the enclosure bottom surface boundary condition on flow patterns and heat transfer characteristics was examined. Both insulated and uniform temperature boundary conditions were considered.

In the second set of experiments, a new chamber with the protrusions oriented vertically was assembled and effects of component orientation on the heat transfer characteristics were examined. In addition, timewise variations of temperature in several locations were measured and interpreted at different power levels.



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TABLE OF SYMBOLS AND ABBREVIATIONS

Symbol	Description	Units
A	Area	m ²
α	Thermal diffusivity	m ² /sec
β	Volumetric expansion coefficient	1/K
c_p	Specific heat	J/kg-°C
emf	Thermocouple voltage	volt
g	Acceleration of gravity	m/sec ²
Gr	Grashof number	Dimensionless
h	Heat transfer coefficient	W/m²-°C
k	Thermal conductivity	W/m-°C
L	Characteristic length	m
L1	Component length in the vertical direction	m
L2	Summation of the ratios of the component fluid exposed areas to their perimeters	m
Nu	Nusselt number	Dimensionless
Nu l	Nusselt number with length scale L1	Dimensionless
Nu2	Nusselt number with length scale L2	Dimensionless
ν	Kinematic viscosity	m²/sec
ω	Uncertainty in the variables	Various

Power	Power dissipated by the heaters	w
Pr	Prandtl number	Dimensionless
Qconv	Energy added to the fluid	W
Qin	Energy input to the heaters	W
Q _{loss}	Energy loss by conduction	W
Q net	Net power dissipated by the heater	W
R _c	Total thermal resistance	°C/W
Rp	Resistance of the precision resistor	ohms
Raf	Flux-based Rayleigh number	Dimensionless
Rat	Temperature-based Rayleigh number	Dimensionless
D	Density	kg/m ³
Tavg	Average of component temperature	°C
Tb	Back surface temperature of board	°C
T _c	Average heat exchanger temperature	°C
T_{f}	Average film temperature	°C
T_s	Back surface temperature of the	
	component	°C
T _{sink}	Average temperature of the heat	°C
**	exchangers	
Vh	Voltage Across the Heaters	Volts
Vin	Input voltage	Volts
W	Chamber width	m
W	Unit of power	W



I. INTRODUCTION

A. STATEMENT OF THE PROBLEM

With the increase in circuit packaging density associated with the miniaturization of microelectronic components, heat dissipation has become a major problem in the design and construction of digital computers and high-power electronic equipment in general. Several alternatives to the solution of the problem have been studied in the past 10 years, including that of Chu [Ref. 1]. Among these, immersion cooling appears to be one of the most effective for achieving high heat-transfer coefficients.

B. IMMERSION COOLING: ANALYTICAL AND EXPERIMENTAL STUDIES

From the construction of the first electronic digital computer, the solution to the problem of heat dissipation from high packaging density electronic equipment has not been easy. Even though very interesting forced convection methods have been studied and very frequently used (Chu [Ref. 1] describes several methods of air- and water-forced convection cooling), the hardware that has to be added to supply the additional power and to store and circulate the cooling liquid can be cumbersome in any application.

The direct immersion of the electronic circuitry into dielectric liquids improves its cooling capability significantly. Baker [Ref. 2] found liquid cooling by free convection to be more than three times as

effective as free convective air cooling of the same device. He made heat transfer measurements from thin-film tantalum nitride resistors evaporated on Corning 7059 glass substrates. The substrates were 1.0 by 2.6 by 0.12 cm. All resistors were rectangular, with their height (dimension parallel to the flow) one-half their base. The surface areas of the resistors were 0.0106, 0.104, 0.477, and 2.00 cm². Two liquids were used in the study: freon with a Prandtl number of 3.9, and Dow Corning #200 silicone dielectric liquid with a Prandtl number of 126. The results showed that the heat transfer coefficient is approximately proportional to the cube root of the reciprocal of viscosity. It was also found that the convection coefficient does increase significantly as the source size decreases. The free convection heat transfer coefficient for the smallest source was more than an order of magnitude greater than for the largest source operated under the same conditions.

In a following study, Baker [Ref. 3] also examined different cooling techniques, such as nucleate boiling, forced convection, and bubble-induced mixing for cooling small heat sources.

Park and Bergles [Ref. 4] conducted experimental studies of natural convection from discrete flush-mounted rectangular heat sources on a circuit board substrate. Micro-electronic circuit elements were simulated with thin foil heaters supplied with DC power. Measurements were also made for protruding heaters of varying widths, in water and R-113. They found and documented the increase in heat transfer coefficient with decreasing width. This effect was greater in R-113 than in water. Also, for protruding heaters, the heat transfer

coefficients for the upper heaters in an array were found to be higher than those for the lower heaters. This behavior was not observed for flush-mounted heaters. As the distance between heaters increased, so did the heat transfer coefficients.

Chen, et al. [Ref. 5] made an experimental study of natural convection heat transfer in a liquid-filled rectangular enclosure with 10 protruding heaters from one vertical wall. The top surface of the enclosure maintained at a uniform temperature acted as the heat sink. All other surfaces, except the heater locations, were unheated. The enclosure was 16.7 cm in height, 2.3 cm in width, and 19.6 cm in depth (horizontal z-direction of the heaters). The 10 heaters were 0.8 cm high, 1.11 cm wide, and 19.6 cm deep. The vertical spacing between heaters was equal to the heater height. Distilled water and ethylene glycol were used as working fluids. Experimental results show that the bottom heater (heater 1), except for high Rayleigh number runs, has the highest heat transfer coefficient. The heat transfer coefficients at heaters 7, 8, and 9 are nearly the same and present the lowest values among the heaters. It was also shown that heat transfer coefficient decreases up to heater 7. At high Rayleigh numbers, the top heater (10) has the highest heat transfer coefficients. The flow visualization carried out indicates a core flow within the enclosure and a recirculating cell in the gap between heaters. Approximate measurements of the fluid velocity were provided from the particle traces in the flow visualization.

Keyhani, et al. [Ref. 6] experimentally studied the buoyancy-driven flow and heat transfer in a vertical cavity with discrete flush heat sources on one vertical wall while the other vertical wall was cooled at a constant temperature. This enclosure contained 11 alternatively unheated and flush-mounted rows of isoflux heated strips. The liquid was ethylene-glycol with a Prandtl number of 150.

To examine the flow structure, visualization experiments were conducted for several power inputs. Finely ground aluminum powder (5 to 20 microns in size) was used to visualize the flow. The observed flow for a power input of 10 watts was highly structured except for small regions near the end walls. A primary flow circulating from the hot wall to the cold wall, a secondary flow with the same sense of circulation as the primary flow, and a tertiary flow in the opposite direction of the secondary flow were observed in the photographs taken at this power level. At a higher power level of 40 watts, the flow pattern above the mid-height region of the cavity showed transition from laminar to turbulent flow along the surface with heaters. The downward flow along the cold wall was still laminar. For a fixed power input, the heat transfer coefficient generally decreased with increase in height (or heater number). The rate at which Nusselt number decreased with the increase in heater number was found to be a strong function of the heater location.

Kelleher, et al. [Ref. 7] and Lee, et al. [Ref. 8] studied experimentally and numerically the cooling by natural convection of a water-filled rectangular enclosure with a long heater protruding from one vertical

wall and conducted flow visualization and heat transfer measurements with the heater at three different elevations. They found the two-dimensional flow to be dual-celled, consisting of a buoyancy-driven upper cell, in which the major part of the fluid motion takes place and which accounts for the majority of the convective heat transfer, and a shear-driven lower cell in which the fluid motion arises due to the viscous drag from the upper cell.

Liu, et al. [Ref. 9] used a three-dimensional finite difference method to study the natural convection cooling of an array of chips mounted on a vertical wall of a three-dimensional rectangular enclosure filled with a dielectric fluid Fluorinert FC 75. They found the long time solution to be oscillatory. Maximum chip temperatures were found on the top surfaces of the three top chips. However, these maximum temperatures did not all occur at the same time, but alternated among these three chips as time proceeded in a rather regular fashion. It was also observed that the bottom sink was quite ineffective in removing heat from the enclosure and that the convective circulation was essentially limited to the chip areas.

Joshi, et al. [Ref. 10] carried out an experimental investigation to study the natural convection cooling of a 3 by 3 array of heated protrusions in a rectangular enclosure filled with dielectric fluid FC-75. They observed that at low power levels (0.1 watts), the flow structure was largely determined by the thermal conditions at the enclosure surfaces. With increasing power levels (0.7 to 3.0 watts), an upward flow developed adjacent to each column of components. The flow away

from the elements became strongly three-dimensional and timedependent with increasing thermal inputs. Component surface temperatures were used to obtain a heat transfer correlation over the range of power levels examined.

Liu, et al. [Ref. 11] carried out a three-dimensional numerical study of immersion cooling of a chip array by laminar natural convection in a rectangular enclosure filled with a dielectric liquid. They determined the local temperature responses on the chip surfaces, their dynamic behaviors, and their dependence on the enclosure gap size. It was found that the temperature responses are decidedly oscillatory with wave forms ranging from simple to complex, and that maximum chip surface temperatures occur on the top row of chips for large gap sizes but oscillate among all three rows of chips for small gap sizes.

C. OBJECTIVES

The work reported here is a continuation of thesis research conducted at the Naval Postgraduate School by Pamuk [Ref. 12] and Benedict [Ref. 13]. The numerical studies by Liu, et al. [Ref. 9] and Liu, et al. [Ref. 11] were the motivation for some of the specific investigations carried out.

The objectives of the present investigation are twofold: The first is to examine the effect of bottom surface boundary condition on thermal transport in the natural convection cooling of a 3 by 3 array of horizontally arranged protruding elements on a vertical wall. The second objective is to examine heat transfer, fluid flow characteristics,

and the influence of the width of the chamber during the natural convection cooling of a 3 by 3 array of vertically arranged protruding elements on a vertical wall. Temperature fluctuation measurements were plotted and compared with existing numerical analysis of Liu, et al. [Refs. 9 and 11] and Benedict [Ref. 13]. For both studies, flow visualizations were also carried out.

II. EXPERIMENTAL SET-UP

A. GENERAL CONSIDERATIONS

Two different experimental configurations were used for the studies reported here. In the first, a 3 by 3 array of rectangular elements with the largest dimension aligned horizontally was examined. In the second study, the largest dimensions were in the vertical direction. The two experimental configurations are next described.

The details of the experimental procedures are available in Benedict [Ref. 13]. The Data Acquisition Programs were the same as used by Pamuk [Ref. 12] and Benedict [Ref. 13] with minor modifications in output format and number of channels. These programs are collected in Appendix D.

1. Experimental Set-Up for the Horizontal Arrangement

A schematic sketch of the arrangement is provided in Figure 2.1 (after Benedict [Ref. 13]). The configuration is the same as the one used by Joshi, et al. [Ref. 9] and Benedict [Ref. 13]. The distribution of the components and the top view of the chamber are illustrated in Figures 2.2 and 2.3 (both after Benedict [Ref. 13]).

This part of the thesis examines the effect of changing the enclosure bottom surface boundary condition on the overall thermal behavior of the system. A more detailed description of the experimental arrangement can be found in Benedict [Ref. 13].

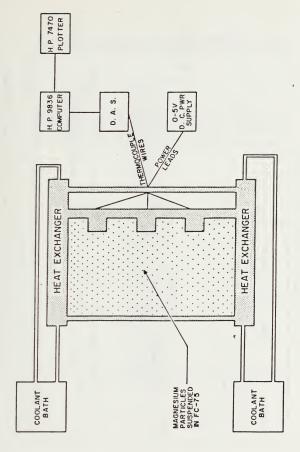


Figure 2.1 Schematic of Entire Assembly

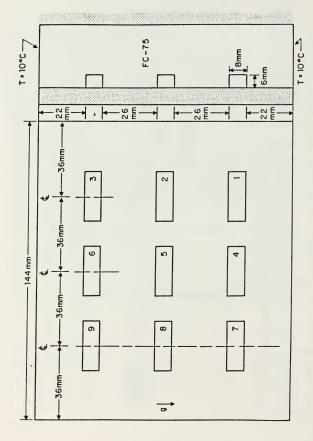


Figure 2.2 Simulated Circuit Card for the Horizontal Arrangement

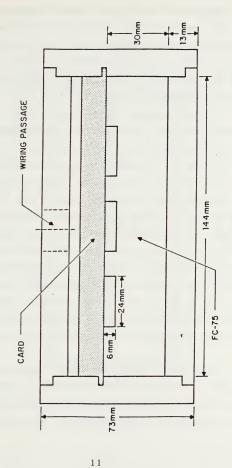


Figure 2.3 Top View of Horizontally Arranged Components Chamber

2. Experimental Set-Up for the Vertical Arrangement

The chamber assembly, illustrated in Figure 2.4 was made of 19.05 mm plexiglass with dimensions of 241.13 mm length, 152.0 mm height, and 120.65 mm width. As in the first arrangement, the chamber was filled with FC-75, a dielectric fluid through tubing at the bottom of the chamber.

In both experimental configurations, two heat exchangers, one at the top and one at the bottom, were used (see Figure 2.1). The design of the exchangers for the first configuration is described in Joshi, et al. [Ref. 10]. In the second study, several modifications were made to reduce the heat transfer from the outside environment to the colder circulating water. The resulting design is seen in Figure 2.5. The external walls of both top and bottom heat exchangers were made of plexiglass. The walls acting as the top and bottom of the fluid-filled enclosure were aluminum plates 3 mm thick, chosen to provide an almost isothermal surface condition. Inlet and outlet headers were provided for flow distribution. Three thermocouples, symmetrically placed along the plate length, were used for the calculation of the average surface temperatures. The heat exchangers could be accessed easily to block one or more of the channels to reduce the coolant flow rates.

A 3 by 3 array of discrete protrusions, vertically arranged (see Figure 2.6), was mounted on a $19.05 \, \text{mm}$ thick plexiglass card. The card was slid into the chamber and was kept in location by plexiglass supports that prevented its linear movement as well as rotation.

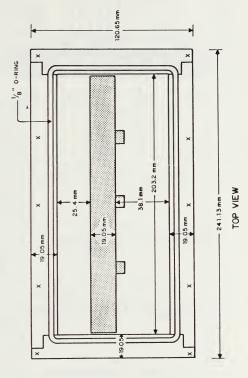


Figure 2.4 Chamber Assembly for the Vertical Arrangement

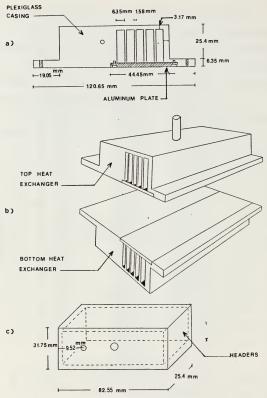


Figure 2.5 Heat Exchangers

(a) Cross-Sectional View;(b) Isometric View;(c) Inlet and Outlet Headers

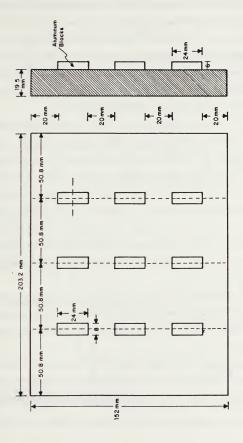


Figure 2.6 Simulated Circuit Card for the Vertical Arrangement

The chamber design allowed the replacement of the card in a simple way. The upper heat exchanger could be removed and the new card could be easily installed. This permits the installation of different card configurations (staggered, flush mounted, etc.) in the future without much additional effort. By moving the card back or forth, the chamber width could be changed. This was done in order to study the effect of this parameter in the overall heat transfer.

The heated components in both studies were aluminum blocks of 8 mm by 24 mm and 6 mm high (see Figure 2.7—after Benedict [Ref. 13]). The dimensions and geometry simulate approximately a 20-pin dual-in-line-package. A nearly uniform heat flux condition was maintained at the base of each block by attaching a foil-type heater with a resistance of about 11 ohms. The foil heaters contained a network of Iconel foil mounted on a Kapton backing and were 23.6 mm by 7.6 mm in dimension and were bonded to the base of each aluminum block using a high thermal conductivity epoxy (Omega Bond 101).

Temperatures at the center of each fluid exposed component face were determined using .127 mm diameter copper-constantan thermocouples. Thermocouple locations on each heater are illustrated in Figure 2.7.

All the thermocouples were connected to an HP-3497 automatic data acquisition system controlled by an HP-9826 microcomputer. Power to the heaters was supplied by a 0-40 volt, 0-1A DC

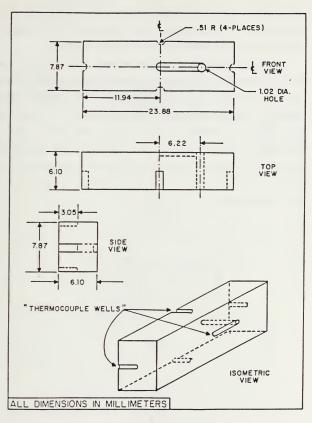


Figure 2.7 Heating Element and Thermocouple Location

power supply. A simultaneous measurement of the overall voltage drop, along with the voltage drop across each heater, allowed the computation of the power dissipation through individual heaters.

Flow visualization was carried out with a 4 mw Helium-Neon laser for illumination. To produce a plane of light, a cylindrical lens was used (see Figure 2.8—after Benedict [Ref. 13]). The laser sheet illuminated magnesium particles (specific gravity of 1.74) that were added to the FC-75 (specific gravity of 1.76 at 25° C). This technique allowed for the visualization of a single two-dimensional plane of the flow field. Time exposure photographs of the flow were obtained using a Nikon F-3 camera with a 50 mm lens, a MD-4 motor drive, and a MT-2 intervalometer.

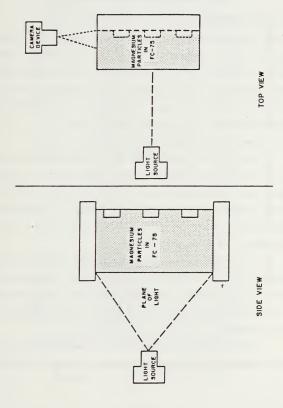


Figure 2.8 Flow Visualization Set-Up

III. RESULTS AND DISCUSSIONS FOR HORIZONTAL ARRANGEMENT

A. FLOW PATTERNS

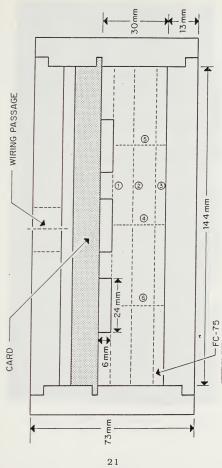
Flow visualization was carried out in six vertical planes, seen in Figure 3.1 (after Benedict [Ref. 13], for the two different bottom boundary conditions: 20° C and insulated. The three-dimensional transport responses, across the range of power dissipation of 0.1 W to 3.0 W, were inferred from these visualizations. In the following, a detailed description of the observed flows is provided.

1. Flow Patterns for the Bottom Boundary at 20° C

The flow patterns observed at several power dissipation levels from no dissipation to 3.0 W are collected in Figures 3.2 to 3.7. Visualization with no power (see Figures 3.2 and 3.3) was to examine the natural convection flow due only to the difference in temperature between the two heat exchangers, and its possible influence on the flow patterns, with the heaters turned on.

At no power, the flow consisted of a single clockwise cell that occupied the entire chamber. This overall flow was established as a result of the temperature differences between the enclosure walls. The three-dimensionality of the flow was evident from visualizations in the various planes.

At 0.1 W, the pattern observed at no power in Figures 3.2 and 3.3 was completely distorted and no remains of the strong clockwise



The six vertical flow visualization planes are identified in the sketch.

Figure 3.1 Top View of the Enclosure With the Card Placed in Position

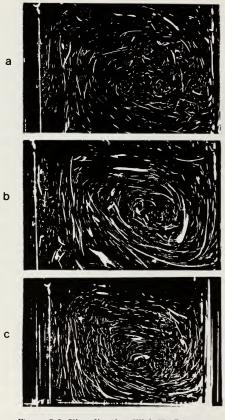


Figure 3.2 Visualization With No Power in Planes 1 (a), 2 (b), and 3 (c)

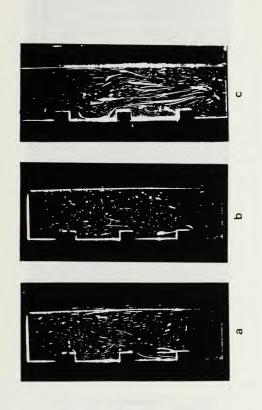


Figure 3.3 Visualization With No Power in Planes 4 (a), 5 (b), and 6 (c)

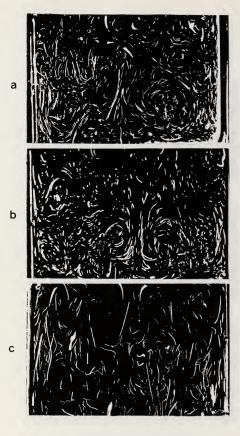


Figure 3.4 Visualization with 1.1 W in Planes 1 (a), 2 (b), and 3 (c)

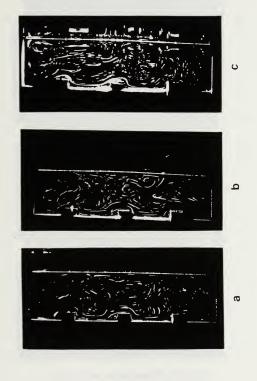


Figure 3.5 Visualization With 1.1 W in Planes 4 (a), 5 (b), and 6 (c)

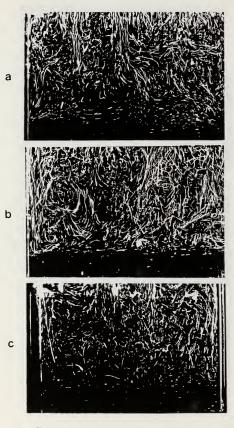


Figure 3.6 Visualization with 3.0 W in Planes 1 (a), 2 (b), and 3 (c)

Figure 3.7 Visualization With 3.0 W in Planes 4 (a), 5 (b), and 6 (c)

flow were seen. Joshi, et al. [Ref. 10] at the same power level reported two very well defined large clockwise cells, one on each side of the central component column. The present visualization showed that the flow now was completely dominated by the relatively high temperature of the bottom heat exchanger. The effects of the buoyancy forces due to the power dissipation were small except in plane 1 (close to the heaters), where there was a well defined upflow.

In plane 2, the particle traces showed a decrease in velocity. Also, dark regions, as observed in Joshi, et al. [Ref. 10], were seen. These were, however, thinner and not well defined. These nearly quiescent regions appear due to the stable stratification produced by the bottom heat exchanger. Descending fluid from the top is unable to penetrate the colder layer of fluid at the bottom. In plane 3, a downflow resulted due to an increase in the density of the colder fluid, in contact with the upper heat exchanger, at 10° C.

At 1.1 W (see Figure 3.4), a well defined pattern could be observed in planes 1 and 2. Along the central column of heaters, the upflow was wider and stronger than near the adjacent columns. This flow was the result of the interaction of an upflow along the central column, a clockwise flow around the right column (heaters 1, 2, and 3), and a counterclockwise flow around the left column (heaters 7, 8, and 9). In plane 3, a downflow of cold liquid was seen. In Figure 3.5, flow patterns at 1.1 W in planes 4, 5, and 6 are illustrated. It is possible in these pictures to appreciate in a side view the strong upflow adjacent to the components. The basic difference with the flow

pattern found in the study by Joshi, et al. [Ref. 10] at the same power level is still that the inactive zone in the bottom of the chamber is not well defined.

With further increase in the power level, the flow in plane 1 exhibited stronger upflow near the components. The buoyancy forces generated by the power dissipation here were strong enough to extend their influence to planes 2 and 3. At 3.0 W, a very thin, dark layer was still observed at the bottom of the chamber (see Figure 3.6). A view of the flow patterns in planes 4, 5, and 6 is illustrated in Figure 3.7. This figure shows a buoyant fluid layer adjacent to the components. In the remaining chamber, the motion was completely random.

2. Flow Pattern With the Bottom Boundary Insulated

The flow pattern for this condition showed similar trends as discussed in section A.1. The induced flow due to the difference in temperature between the two heat exchangers was not appreciable.

B. HEAT TRANSFER MEASUREMENTS

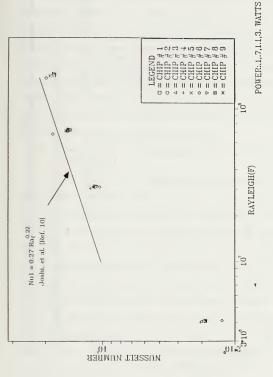
Heat transfer measurements were made at power levels of 0.1, 0.7, 1.1, 1.5, and 3.0 watts for the two bottom surface boundary conditions. The temperature at the top heat exchanger was maintained constant at 10° C in all experiments. Temperature and flux-based Rayleigh numbers (Ra_t and Ra_f) were calculated in a manner identical to that discussed in Joshi, et al. [Ref. 10] and plotted versus Nusselt number (Nu1). These are defined in the Table of Symbols and Abbreviations.

Heat Transfer Measurements With the Bottom Boundary at 20° C

Component surface temperature measurements at various power levels are collected in Tables 1 through 8 in Appendix C. The nondimensional heat transfer parameters in the form of Nusselt versus Rayleigh numbers are illustrated in Figures 3.8 and 3.9. In the same plots, the correlations found by Joshi, et al. [Ref. 10] were also plotted.

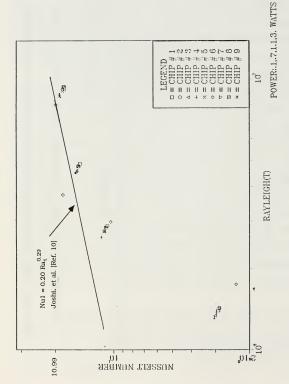
We can see that having the bottom heat exchanger at 20° C results in general in lower Nusselt numbers than those found by Joshi, et al. [Ref. 10] in the range of Rayleigh numbers considered. At higher power levels, when the temperature of the heaters was considerably higher than the bulk temperature of the dielectric fluid, the difference in Nusselt numbers is smaller than at lower power levels. The Nusselt number at a flux-based Rayleigh number of 106 found by Joshi, et al. [Ref. 10] was 20.4, while the Nusselt number obtained here for the same Rayleigh number was 19. At lower power levels 0.1 W and 0.7 W, the differences in Nusselt number were greater, and the decrease in the heat transfer coefficient was significant. The Nusselt number found by Joshi, et al. [Ref. 10] was 10.5 at a flux-based Rayleigh number of 106, while the Nusselt obtained with the present configuration was 2.9.

At power levels of 0.1 W and 0.7 W, a small increase in the upper heaters' temperatures over the lower ones was observed. At higher power levels, the highest temperatures were found irregularly in different components.



Correlation found by Joshi, et al. [Ref.10] is plotted with a continuous line.

Figure 3.8 Plot of Flux-Based Rayleigh Number Versus Nusselt Number



Correlation found by Joshi, et al. [Ref.10] is plotted with a continuous line.

Figure 3.9 Plot of Temperature-Based Rayleigh Number Versus Nusselt Number

The component that presented the largest variations from the mean in the heat transfer coefficients was the upper component in the central column (heater 6). This is evidenced as deviations from the general trend of the obtained data. The variations (lower heat transfer coefficient at low power levels, and higher heat transfer coefficients at higher power levels) are expected because this component receives the influence of the combined upflowing streams (produced by the other heaters), as was observed and documented in the flow visualization results in Section A.1. The effect is greater at higher power levels when the component's temperature is substantially larger than the bottom heat exchanger temperature.

2. Heat Transfer Measurements With the Bottom Boundary Insulated

The results of the temperature measurements with the bottom boundary insulated and the reduced dimensionless parameters are collected in Tables 9 through 16 in Appendix C. In Figures 3.10 and 3.11, flux and temperature Rayleigh numbers versus Nusselt numbers were plotted. Correlations found by Joshi, et al. [Ref. 10] were also plotted for comparison. It was seen that having the bottom heat exchanger insulated improved the cooling at low power levels (0.1 W and 0.7 W) over that obtained with the bottom boundary maintained at 20° C. This result is expected because now the temperature of the bottom boundary was 15° C at 0.1 W and 17° C at 0.7 W. At a power level of 3.0 W, no cooling improvement was observed. The temperature for the bottom boundary at 3.0 W was 22° C.

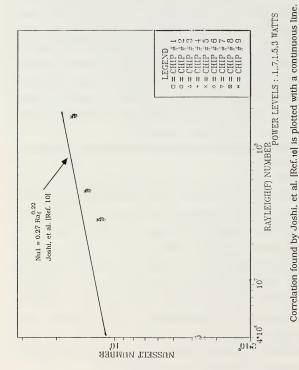
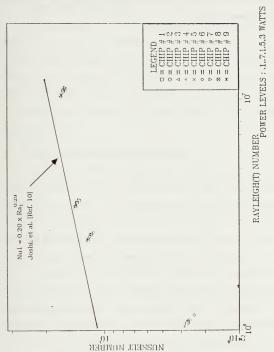


Figure 3.10 Plot of Flux-Based Rayleigh Number Versus Nusselt Number



Correlation found by Joshi, et al. [Ref. 10] is plotted with a continuous line.

Figure 3.11 Plot of Temperature-Based Rayleigh Number Versus Nusselt Number

Comparisons with the correlation obtained by Joshi, et al. [Ref. 10] show a decrease in the heat transfer coefficient when the lower boundary was insulated. This was evidenced by the lower Nusselt numbers at all power levels.

IV. RESULTS AND DISCUSSIONS FOR VERTICAL ARRANGEMENT

A. FLOW VISUALIZATION

The visualization for this experiment was tried for a chamber width of 9 mm. As was expected, there was almost no flow in the narrow gap between components and the front wall. A boundary layer-like behavior was observed on the vertical side faces of the components. The photography process was complicated because the thickness of the plane to be illuminated by the laser sheet for this chamber width was only 3 mm.

B. HEAT TRANSFER MEASUREMENTS

Component surface temperature measurements were made for chamber widths of 30 mm and 9 mm (see Figure 4.1). The power level range was 0.1 W to 3.0 W. Temperatures of the top and bottom boundaries were maintained constant at 10° C. Plots of Nu1 versus Raf are provided for comparisons with data obtained by Benedict [Ref. 13].

1. Heat Transfer Measurement for w = 30 mm

Tables 17 through 28 in Appendix C compile component surface temperature and resulting nondimensional heat transfer data for this gap size with increasing power levels. The mean values of the component averaged temperatures over the nine heated components were 13° C for 0.1 W and 47° C for 3.0 W. In the range 0.1 W to 1.1 W, the lowest T_{avg} levels were on the bottom-row components

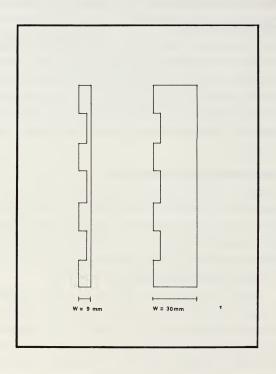


Figure 4.1 Side View Showing the Chamber Widths Used in the Experiment

(components 1, 4, and 7). The observed tendency was that temperatures on specific locations on the components in the top row were higher than those in the same location on the components in lower rows. As was pointed out by Liu, et al. [Ref. 11], the possible reason for this might be that components in the top row are in contact with warmer liquid, and the upper-row components are located in the heated wake regions of the lower rows. Additionally, the stratified fluid away from the components, which feeds fluid toward the component rows, is also at higher temperature for the upper rows.

Analyzing individual components in the middle and lower rows, for all power levels, the minimum measured temperatures were on the bottom surfaces. This trend is also supported by Liu, et al. [Ref. 9]. On the top row components, the lowest temperatures were on either one of the vertical side faces. Maximum temperatures were found generally on the component surface facing the front chamber wall. Liu, et al. [Ref. 11] obtained numerically maximum temperatures in the surfaces facing upward and attributed this to the fact that the heated flow coming off the vertical surfaces reduced the heat transfer coefficient at the component top surface. At higher power levels, oscillations in temperature changed the locations of the maximum and minimum instantaneous values, but the general tendencies found earlier were still noticed.

In Figure 4.2, a plot of Nu1 versus Ra_f is seen. Data obtained from Benedict [Ref. 13] is also plotted. A linear least squares fit to the present measurements in Figure 4.2 was performed. This is given by:

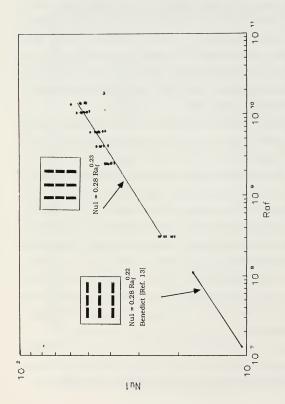


Figure 4.2 Comparison of the Nondimensional Heat Transfer Measurements The curve fit for the horizontal arrangement is from Benedict [Ref. 13]. Present measurements and curve fit are for the vertical arrangement. for Two Different Component Orientations

Nu1 =
$$0.28 \text{ Ra}_{\mathrm{f}}^{0.23}$$
 in the range $3*10^8 < \text{Ra}_{\mathrm{f}} < 10^{10}$ and $15 < \text{Pr} < 30.2$ (4.1)

and the one obtained with the data from Benedict [Ref. 13] was:

Nul = 0.28
$${\rm Ra_f^{0.22}}$$
 in the range $10^7 < {\rm Ra_f} < 2*10^8$ and 15 < Pr < 30.2 $\eqno(4.2)$

Comparisons between Equations 4.1 and 4.2 indicate that Nu appears not to depend on the orientation of the components in the range of Ra_f and Pr considered. This is illustrated in Figure 4.2

2. Heat Transfer Measurement for w = 9 mm

In Tables 29 through 40 in Appendix C, component temperatures and resulting nondimensional heat transfer data are compiled. Decreasing the chamber width from 30 mm to 9 mm produced some increase in the average temperature of the components T_{avg} . This behavior was expected considering that now the surface of both top and bottom heat exchangers has been reduced to 30 percent of its former value. The mean value of the component averaged temperatures over the nine heaters for a power of 0.1 W was 14.5° C, 1.5° C higher than the average temperature obtained with 30 mm width. For a dissipation level of 3.0 W, the mean value of the components' averaged temperature over the nine heaters was 51° C, 4.0° C higher than the average observed for the 30 mm width. The T_{avg} value increased from the bottom to the top row, as was also found for w = 30 mm.

Analyzing individual components on the bottom row (components 1, 4, and 7), minimum temperatures were found on the bottom surfaces.

Plots of Nu1 versus Ra_f are illustrated in Figure 4.3. The correlation obtained for this chamber width was:

Nu1 = 0.073 Ra_f^{0.28} in the range
$$3 * 10^8 < Ra_f < 10^{10}$$

and $15 < Pr < 30.2$ (4.3)

This correlation indicates the expected decrease in Nu1 for the same $Ra_{\rm f}$, when compared with Equation 4.1 for w = 30 mm.

C. TEMPERATURE FLUCTUATIONS IN STEADY STATE

Oscillations in component surface temperatures following achievement of nominally steady conditions were measured in the dissipation range of 0.1 W to 3.0 W. Three thermocouples were scanned at a rate of approximately three times per second for a period of 200 seconds. Plots of surface temperature variations were made in order to display the long-time temperature fluctuations and compare with results of Liu, et al. [Ref. 11] and Benedict [Ref. 13]. Figure 4.4 is a vertical arrangement diagram which portrays the location of the scanned thermocouples.

1. Surface Temperature Fluctuations for a w = 30 mm

Temperature oscillations for this chamber width are illustrated in Figures 4.5 through 4.7. It was observed that at all power

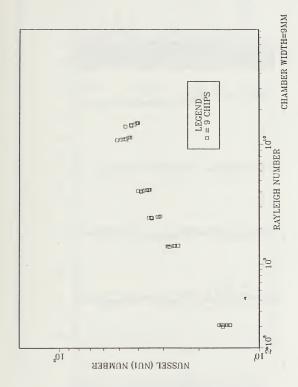
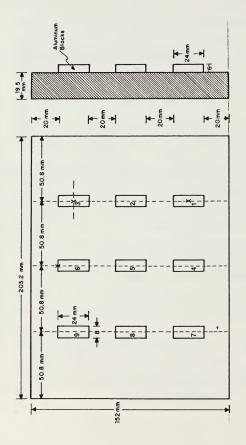
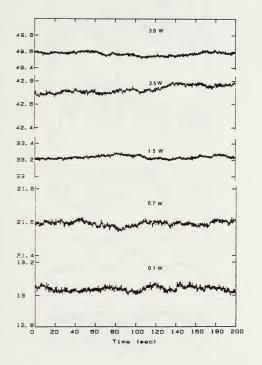


Figure 4.3 Plot of Nu1 vs. Ra $_{\rm f}$ for a Chamber Width = 9 mm



44



 $Figure \ 4.5 \ \ \textbf{Temperature Fluctuations for} \\ \textbf{Thermocouple No. 0 at Different Power Levels}$

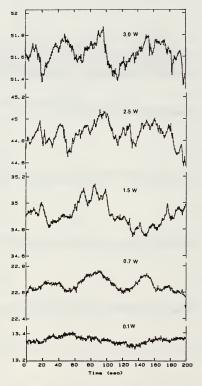
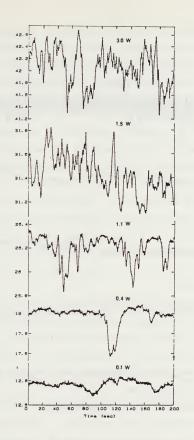


Figure 4.6 Temperature Fluctuations for Thermocouple No. 12 at Different Power Levels



 $Figure \ 4.7 \ \ \textbf{Temperature Fluctuations for} \\ \textbf{Thermocouple No. 31 at Different Power Levels}$

levels considered, there were no temperature fluctuations on the components in the lower row. Benedict [Ref. 13] documented with heat transfer measurement and flow visualizations that the stagnant fluid layer above the bottom heat exchanger prevented the penetration of warmer fluid, resulting in conduction-dominated transport for the bottom row of components.

At 0.1 W, a spread in temperature of less than 0.5° C was observed between the six thermocouples that were scanned. Increasing the power level to 0.7 W, oscillation amplitudes with a mean of 0.7° C were observed in component 6. At 1.1 W, the amplitude increased to 0.8° C. Benedict [Ref. 13] found that a component at the same relative location and power level in a horizontal arrangement had almost no oscillations. At 2.5 W, oscillations of about 1.6° C were found. At 3.0 W, oscillations rose to almost 1.7° C at the same location. Benedict [Ref. 13] found at 3.1 W for the equivalent thermocouple an amplitude of 0.85° C.

2. Surface Temperature Fluctuations for w = 9 mm

Plots of temperature oscillations are illustrated in Figures 4.8 through 4.10. At 0.1 W, no fluctuations were found in any of the thermocouples scanned. At 0.4 W, fluctuations of 0.3° C were observed in the top row components. No fluctuations were observed in the middle and bottom row components.

Increasing the power dissipation level to 0.7 W, no fluctuations were observed in either the middle or the bottom rows, but

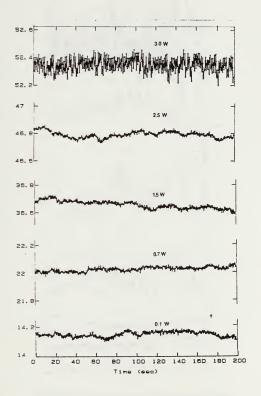


Figure 4.8 Temperature Fluctuations for Thermocouple No. 0 at Different Power Levels

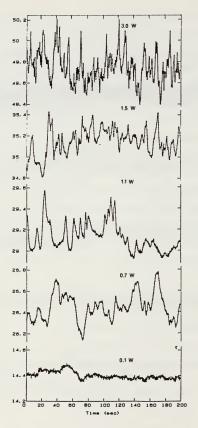
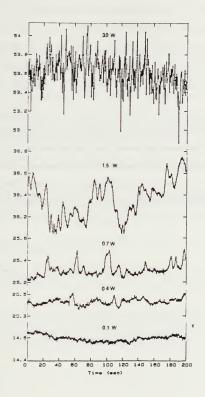


Figure 4.9 Temperature Fluctuations for Thermocouple No. 12 at Different Power Levels



 $\label{eq:Figure 4.10} \begin{tabular}{ll} Figure 4.10 & Temperature Fluctuations for \\ Thermocouple No. 31 & Different Power Levels \\ \end{tabular}$

fluctuations of 0.7° C were observed in the top row. At 1.1 W, fluctuations in the top-row components were about 0.9° C. No fluctuations were observed at the middle and bottom rows. At 1.5 W, fluctuations of 0.2° C appeared in the components in the middle row and reached values of 1.1° C in the top-row components. At 3.0 W, the highest power level utilized in the experiments, fluctuation amplitudes on the top-row components were recorded at 2.0° C. It is interesting to note that no significant increase in the amplitude of the fluctuations was observed when the chamber width was changed from 30 mm to 9 mm. Liu, et al. [Ref. 11] calculated temperature oscillations peak to valley of 8° C for the 9 mm chamber width. They attributed the increase in the oscillation amplitude to the fact that now the flow is highly confined.

V. RECOMMENDATIONS

The design of the present chamber can be improved in many ways to give more versatility in the following experiments. The recommended changes that can be made to software and hardware include:

- Placement of the blocks can be done by screwing or attaching them to the board in a different way to the one used until now, which is bonding the chips to the board with glue. This would allow the experimenter to change a defective heater or change the orientation of the chips for a different set of experiments, using the same board and the same equipment set-up.
- To avoid the flow of dielectric liquid to the back of the chamber through the gaps between the board and the chamber walls that can alter the heat transfer results or the flow visualization, a small diameter O-ring can be used. A groove should be engraved in the board to allow the O-ring installation.
- Temperature measurements within the fluid and on the board surfaces should also be performed.
- a Fast Fourier Transform algorithm should be developed to perform frequency analysis on the surface temperature fluctuations data. In addition, improvements in the plotting programs can be made.
- With the present set-up, different combinations of heaters could be powered, row-wise or column-wise or staggered, instead of the entire array. This variation might help better to explain the heat transfer and flow characteristics of the chamber.

APPENDIX A

SAMPLE CALCULATIONS

A. CONVERSION OF THERMOCOUPLE VOLTAGES TO TEMPERATURES

(Channels 0 to 60 and 71 to 76, in the data acquisition system)

where D1 to D9 are the calibration coefficients of the Omega thermocouples and are: 0.10086091, 25727.9, -767345.8, 7802-5596, -9247486589, 6.98E11, -2.66E13, and 3.94E14.

Calculating the temperature found in the thermocouple connected to channel 0 at 1.1 W gives:

Emf = 0.995E-3 V

 $T = 24.48^{\circ} C$

B. CALCULATION OF HEATER POWER

Channels 61 to 70 in the data acquisition system are used to measure the supply voltage (61) and voltage to the heaters.

Power = Emf * (Volt - Emf)/Rp

Calculating the power dissipated by the heater #3:

C. CALCULATION OF THE DIMENSIONLESS PARAMETERS

1. Calculation of the Block Faces Areas

Dimensions of the aluminum blocks are: length 24 mm, width 8 mm, and thickness 6 mm.

$$A_{cen} = 24 \text{ mm} * 8 \text{ mm} = 192 \text{ mm}^2 = 1.92\text{E-4 m}^2$$
 $A_{lef} = 24 \text{ mm} * 6 \text{ mm} = 144 \text{ mm}^2 = 1.44\text{E-4 m}^2$
 $A_{rig} = 24 \text{ mm} * 6 \text{ mm} = 144 \text{ mm}^2 = 1.44\text{E-4 m}^2$
 $A_{top} = 6 \text{ mm} * 8 \text{ mm} = 48 \text{ mm}^2 = 4.8\text{E-5 m}^2$
 $A_{bot} = 6 \text{ mm} * 8 \text{ mm} = 48 \text{ mm}^2 = 4.8\text{E-5 m}^2$
 $A_{tot} = \Sigma A = 576 \text{ mm}^2 = 5.76\text{E-4 m}^2$
 $T_{avg} = \Sigma (T(I) * A(I))/A_{tot}$

Calculating for component 3 at 1.1 W:

$$T_{avg} = (27.67 * 1.92E-4 + 25.73 * 4.8E-5 + 26.08$$

$$* 1.44E-4 + 26.69 * 4.8E5) / 5.76E-4$$

$$T_{avg} = 26.63^{\circ} \text{ C}$$

2. Calculation of the Temperatures at the Back of the Components

Due to problems in the placement of the thermocouples that measure the temperature at the heaters, these temperatures were calculated with a calibration curve for $w=30\,\mathrm{mm}$ from data obtained in Benedict [Ref. 13]. This calibration cannot be applied to the case where the width of the chamber is very small. In such a case, when $w=9\,\mathrm{mm}$, a one-dimensional conduction analysis was applied to find the back temperature.

The best fit for the calibration points was:

$$T(K) = 14.003957 * Power + 14.517501$$

So, for 1.1 W,

$$T = 29.92^{\circ} C$$

To Calculate the Conduction Losses Through the Circuit Card

$$\begin{split} Q_{loss} &= \Delta T/Rc = 1/N \ \Sigma(T(l) - Tb(J))/Rc \\ R_c &= L/kA \\ R_c &= 19.5E\text{-}3/(0.195 * 8E\text{-}3 * 24E\text{-}3) = 520.83 \ K/W \\ L &= 19.5E\text{-}3 \ m \\ k &= 0.195 \ W/m.K \ (plexiglass conductivity [Ref. 14]) \\ A &= (24E\text{-}3 * 8E\text{-}3) \ m^2 = 1.92E\text{-}4 \ m^2 \\ Q_{loss} &= (29.92 - 17.31)/520.83 \\ &= 0.024 \ W \end{split}$$

4. To Find the Average Sink Temperature

Channels 58, 59, and 60 in the bottom heat exchanger and channels 61, 72, and 73 in the top heat exchanger.

$$\begin{split} T_{sink} &= 1/N \; (\Sigma T_{tc} + \Sigma T_{bc}) \\ T_{sink} &= (10.05 + 10.1 + 10.02 + 10.11 + 10.12 + 10.13)/6 \\ T_{sink} &= 10.08^{\circ} \; C \end{split}$$

To find the net power dissipated by the heater, Qnet:

For 1.1 W and component 3:

$$Q_{\text{net}} = (1.1 - 0.024) \text{ W}$$

= 1.076 W

To find the convection coefficient h (from Newton's law of cooling):

$$Q_{net} = h * A_{tot} * \Delta T$$
 $\Delta T = T_{avg} - T_{sink}$
 $\Delta T = (26.63 - 10.08)^{\circ} C$
 $T = 16.55^{\circ} C$
 $h = Q_{net} / (A_{tot} * \Delta T)$

5. For 1.1 W and Component 3

$$h = 1.09 / (16.55 * 5.76E-4)$$

 $h = 114.342 \text{ W/m}^2 \text{ K}$

6. To Calculate the Thermal Conductivity of the FC-75

$$k = (0.65 - 7.8947E-4 * T_{film})/10$$

where $T_{film} = (T_{avg} + T_{sink})/2$.

At 1.1 W and chip 3:

$$T_{film} = (26.63 + 10.08)^{\circ} C/2$$

 $T_{film} = 18.35^{\circ} C$

k = 0.0645 W/m K

 To Calculate the Vertical Length Based Nusselt Number, Nu1

$$Nul = h * L1/k$$

Nu1 = 114.342 * 24E-3/0.0645

Nu1 = 42.54

 To Calculate the Ratio Area/Perimeter Based Nusselt Number, Nu2

 $L2 = \Sigma(A(i)/P(i))$

$$L2 = (24 * 8)/64 + (2 * 8 * 6)/(2 * 14) + (2 * 24 * 6)/(2 * 60)$$

L2 = 11.229E-3 m

L2 = 19.905

9. To Calculate the Density of the FC-75, p (Kg/m3)

$$\rho = (1.825 - 0.00246 * T_{film}) * 1000$$

 $\rho = 1779.86 \text{ Kg/m}^3$

10. To Calculate the FC-75 Specific Heat, Cp (J/Kg K)

$$Cp = (.241111 + 3.7037E-4 * T_{film}) * 4180$$

 $Cp = 1036.25 \text{ J/Kg K}$

11. To Calculate the FC-75 Viscosity, v(m²/s)

$$v = (1.4074 - 2.964E-2 * T_{\rm film} + 3.8018E-4 \\ * T_{\rm film}^2 - 2.7308E-6 * T_{\rm film}^3 + 8.1679E-9 * T_{\rm film}^4)E-6 \\ v = .97557E-6 \; {\rm m^2/s}$$

12. To Find the FC-75 Thermal Expansion Coefficient, $\beta(K^{-1})$

$$\beta = 0.00246/(1.825 - 0.00246 * T_{film})$$

For 1.1 W and component 3:

$$\beta = 1.382E-3 K-1$$

13. To Calculate the FC-75 Thermal Diffusivity $\alpha(m^2/s)$

$$\alpha = k/\rho * Cp$$

For 1.1 W and component 3:

$$\alpha = 3.497E-8 \text{ m}^2/\text{s}$$

14. To Calculate the Grashof Number

$$Gr = g * \beta * 1^3 * \Delta T/v^2$$

For 1.1 W and component 3:

15. To Calculate the Prandtl Number

$$Pr = v/\alpha$$

$$Pr = 27.89$$

16. To Find the Temperature Based Rayleigh Number

$$Ra = Gr * Pr$$

For 1.1 W and component 3:

$$Ra = 9.08E7$$

17. To Calculate the Flux Based Rayleigh Number

$$Ra_f = g * B * 1^4 * Q_{net}/(k * v * \alpha * A_{tot})$$

$$Ra_f = 3.9E9$$

APPENDIX B

UNCERTAINTY ANALYSIS

The uncertainty analysis was done using the method of Kline and McClintock, presented in Holman [Ref. 15]. The calculations will be done for the end values 0.1 W and 3.0 W, for a chamber width of 30 mm.

A. UNCERTAINTIES IN THE NET POWER ADDED TO THE FLUID

$$Q_{net} = Power - Q_{loss}$$

$$Power = emf(I) * (Volt - emf(I))/Rp$$

Power =
$$f(emf(I), Volt, Rp)$$

$$\frac{\partial Power}{\partial emf(1)} = \frac{Volt - 2 \cdot emf(1)}{Rp}$$

$$\frac{\partial Power}{\partial Volt} = \frac{emf(I)}{Rp}$$

$$\frac{\partial Power}{\partial Rp} = -\frac{emf(I) \cdot (Volt - emf(I))}{Rp^2}$$

$$W_{\text{power}} = \left[\left(\frac{\partial_{\text{power}}}{\partial_{\text{emf}(1)}} \right)^{2} W_{\text{emf}(1)}^{2} + \left(\frac{\partial_{\text{power}}}{\partial_{\text{Volt}}} \right)^{2} W_{\text{Volt}}^{2} + \left(\frac{\partial_{\text{power}}}{\partial_{\text{Rp}}} \right)^{2} W_{\text{Rp}}^{2} \right]^{\frac{1}{2}}$$

$$W_{\rm emf} = 0.001 \text{ V}$$

(by Resolution in the reading and precision of measuring devices)

$$W_{\text{Volt}} = 0.001 \text{ V}$$

(by Resolution in the reading and precision of measuring devices)

$$W_{\text{Rp}} = 0.05 \ \Omega$$

(including the added resistances)

For 0.1 W and chip 3:

$$emf(I) = 1.022 V$$

$$Volt = 1.225 V$$

$$Rp = 2.06 \Omega$$

(measured resistance including resistances in the junctions, etc.)

$$\frac{\partial \text{Power}}{\partial \text{emf(I)}} = -0.397$$

$$\frac{\partial \text{Power}}{\partial \text{Volt}} = 0.496$$

$$\frac{\partial \text{Power}}{\partial \text{Rp}} = -0.0488$$

$$W_{\text{power}} = \left[\left(-0.397 \right)^2 \cdot \left(0.001 \right)^2 + \left(0.496 \right)^2 \cdot \left(0.001 \right)^2 + \left(-0.0488 \right)^2 \cdot \left(0.05 \right)^2 \right]^{\frac{1}{2}}$$

$$W_{power} = 0.00252 \text{ W}$$

$$\frac{W_{\text{power}}}{\text{Power}} = \frac{0.00252 \,\text{W}}{0.1 \,\text{W}} = 2.5 \,\%$$

$$Q_{loss} = \frac{\Delta T}{Rc}$$

where ΔT is the difference in temperature between the back surface of the chip and the back of the board.

$$Q = f(\Delta T, Rc)$$

$$\frac{\partial Q_{loss}}{\partial \Delta T} = \frac{1}{Rc} = \frac{Q_{loss}}{\partial Rc} = \frac{\Delta T}{Rc^2}$$

For 0.1 W and component 3:

$$\frac{\partial Q_{loss}}{\partial \Delta T} = \frac{1}{520.83 \text{ K/W}} = 0.00192$$

$$\frac{\partial Q_{loss}}{\partial Rc} = -\frac{0.12^{\circ} K}{(520.83)^{2}} = -4.424 \times 10^{-7}$$

$$WQ_{loss} = \left[\left(\frac{l}{Rc} \right)^2 W_{\Delta T} + \left(\frac{-\Delta T}{Rc^2} \right) W_{Rc} \right]$$

$$W_{\Delta T} = 10\% = 0.012^{\circ} \text{ C}$$

$$W_{Rc} = 10\% = 52.083 \text{ K/W}$$

$$WQ_{loss} = \left[(0.00192^{2} \cdot 0.012^{2} + (-4.424 \times 10^{-7})^{2} \cdot (52.083)^{2} \right]^{\frac{1}{2}}$$

$$WQ_{loss} = \left(5.352 \times 10^{-10} \right)^{\frac{1}{2}} = 3.258E - 5$$

$$\frac{WQ_{loss}}{Q_{loss}} = 0.14 = 14\%^{1}$$

$$WQ_{net} = \left[(W_{power})^{2} + (WQ_{loss})^{2} \right]^{\frac{1}{2}}$$

$$WQ_{net} = \left[(0.00252)^{2} + (3.258 \times 10^{-5})^{2} \right]^{\frac{1}{2}}$$

$$WQ_{net} = \pm 0.025 \text{ W}$$

$$\frac{WQ_{net}}{Q}_{net} = \pm 2.5\%$$

¹The uncertainties in the losses are relatively big, but they do not have a large effect on the final undertaking.

For 3.0 W and component 3:

$$emf(I) = 5.647 V$$

$$Volt = 6.762$$

$$Rp = 2.06\Omega$$

$$\frac{\partial \text{Power}}{\partial \text{emf(I)}} = -2.2$$

$$\frac{\partial \text{Power}}{\partial \text{Volt}} = 2.74$$

$$\frac{\partial \text{Power}}{\partial \text{Rp}} = 1.484$$

$$W_{\text{power}} = \left[\left(-2.2 \right)^2 \cdot \left(0.00 \right) \right]^2 + \left(2.74 \right)^2 \cdot \left(0.00 \right)^2 + \left(1.484 \right)^2 \cdot \left(0.05 \right)^2 \right]^{\frac{1}{2}}$$

$$W_{\text{power}} = 0.74 \text{ W}$$

$$\frac{W_{\text{power}}}{\text{power}} = \frac{0.074}{3.0} = \pm 2.5\%$$

$$\frac{\partial Q_{loss}}{\partial \Delta T} = \frac{1}{520.83} k/w = 0.00192$$

$$\frac{\partial Q_{loss}}{\partial Rc} = -\frac{21.68}{(520.83)^2} = -7.993E - 5$$

$$WQ_{loss} = \left[(0.00192^{2} \cdot (2.168)^{2} + (-7.992E - 5)^{2} \cdot (52.083)^{2} \right]^{\frac{1}{2}}$$

$$WQ_{loss} = 0.059 \text{ W}$$

$$\frac{WQ_{loss}}{Q_{.}} = 14.14\%$$

$$WQnet = \left[\left(W_{power} \right)^{2} + \left(WQ_{loss} \right)^{2} \right]^{\frac{1}{2}}$$

$$WQnet = \left[(0.074)^{2} + (0.0059)^{2} \right]^{\frac{1}{2}}$$

$$WQ_{net} = \pm 0.0742 \text{ W}$$

$$\frac{WQ_{\text{net}}}{Q_{\text{net}}} = \pm 2.5\%$$

B. UNCERTAINTY IN RAYLEIGH AND NUSSELT NUMBERS Starting with:

$$Q_{net} = hA_{tot} (T_{avg} - T_{sink})$$

$$h = \frac{Q_{net}}{A_{tot} (T_{avg} - T_{sin k})}$$

$$h = f(Q_{net}, A_{tot}, \Delta T)$$

$$\frac{\partial h}{\partial Q_{\text{net}}} = \frac{1}{A_{\text{tot}}(\Delta T)}$$

$$\frac{\partial h}{\partial A_{tot}} = \frac{Q_{net}}{A_{tot}(\Delta T)^2}$$

$$\frac{\partial h}{\partial \Delta T} = \frac{Q_{\text{net}}}{A_{\text{tot}} (\Delta T)^2}$$

for 0.1 W and component 3:

$$A_{tot} = 5.76 \times 10^{-4} m^2$$
 (for all components)

$$\frac{\partial h}{\partial Q_{\text{net}}} = \frac{1}{(5.76 \times 10^{-4})(3.02)} = 574.87$$

$$\frac{\partial h}{\partial A_{tot}} = \frac{0.1}{(5.76 \times 10^{-4})(3.02)} = -99804.03$$

$$\frac{\partial h}{\partial \Delta T} = -\frac{-0.1}{\left(5.76 \times 10^{-4}\right) \left(3.02\right)^2} = -19.035$$

$$W\mathbf{h} = \left[\left(\frac{\partial \mathbf{h}}{\partial \mathbf{Q}_{\mathrm{net}}} \right)^{\!\!2} \! W \mathbf{Q}_{\mathrm{net}}^{2} \right. \\ \left. + \left(\frac{\partial \mathbf{h}}{\partial \Delta_{\mathrm{tot}}} \right)^{\!\!2} \! W_{\mathrm{A}_{\mathrm{tot}}}^{2} \right. \\ \left. + \left(\frac{\partial \mathbf{h}}{\partial \Delta \mathrm{T}} \right)^{\!\!2} \! W_{\Delta \mathrm{T}}^{2} \right]^{\!\!\frac{1}{2}}$$

$$WQ_{\text{net}} = \pm 0.0025 \text{ W}$$

$$W_{\rm L} = \pm 10^{-5} {\rm m}$$

$$W_{\text{A}} = \left[\left(10^{-5} \right)^2 + \left(10^{-5} \right)^2 \right]^{\frac{1}{2}} = 1.4 \text{ lE } -5 \text{ m}^2$$

$$W_{\rm AT} = \pm 1\% = 0.03^{\circ} \, {\rm C}$$

$$W_{\rm h} = \left[\left(574.87 \right)^2 \cdot \left(0.0025 \right)^2 + \left(99804 \right)^2 \cdot \left(1.4 \, \text{IE} - 5 \right)^2 + \left(19.035 \right)^2 \cdot \left(0.03 \right)^2 \right]^{\frac{1}{2}}$$

$$W_{\rm h} = (2.065 + 0.019 + .3260)^{\frac{1}{2}}$$

$$= \pm 2.09 \text{ W/m}^2 \text{ K}$$

$$\frac{W_h}{h} = \frac{2.09}{57.487} = \pm 3.64\%$$

For 3.0 W and component 3:

$$\frac{\partial h}{\partial Q_{\text{net}}} = \frac{1}{(5.76 \times 10^{-4})(38.38)} = 45.52$$

$$\frac{\partial h}{\partial A_{tot}} = \frac{3.0}{\left(5.76 \times 10^{-4}\right)^2 (38.38)} = 235597.84$$

$$\frac{\partial h}{\partial \Delta T} = \frac{3.0}{\left(5.76 \times 10^{-4}\right) \left(38.38\right)^2} = 3,536$$

$$W_{\rm h} = \left[\left(45.52\right)^2 \cdot \left(0.0742\right)^2 + \left(235597.8\right)^2 \cdot \left(1.4\,\text{IE} - 5\right)^2 + \left(3.54\right)^2 \cdot \left(.38\right)^2 \right]^{\frac{1}{2}}$$

$$W_h = \pm 4.92 \text{ w/m}^2 \text{ K}$$

$$\frac{W_h}{h} = \frac{4.92}{135.7} = 3.63\%$$

To find the uncertainty of Nusselt Number:

$$Nu = \frac{h_L}{k}$$

$$Nu = f(h, L, k)$$

$$\frac{\partial Nu}{\partial h} = \frac{L}{k}$$

$$\frac{\partial Nu}{\partial L} = \frac{h}{k}$$

$$\frac{\partial Nu}{\partial k} = -\frac{hL}{k^2}$$

Since the thermal properties of the FC-75 (dielectric liquid) are values that depend on film temperatures, it is considered that there are no uncertainties in these values.

$$K = (0.65 - 7.89474E - 4 \cdot T_{film})/10$$

$$T_{\rm film} \, = \frac{T_{\rm avg} \, + T_{\rm sin \, k}}{2}$$

For 0.1 W and component 3:

$$K = 0.064 \frac{W}{m K}$$

$$\frac{\partial Nu}{\partial k} = \frac{24 \times 10^{-3} \text{m}}{0.064 \text{ w/m K}} = 0.374$$

$$\frac{\partial Nu}{\partial k} = \frac{57.487}{24 \times 10^{-3}} = 2395.29$$

$$\frac{\partial Nu}{\partial k} = \frac{57.487 \times 24 \times 10^{-3}}{(0.064)^2} = 336.84$$

$$W \mathrm{Nu} = \left[\left(\frac{\partial \mathrm{Nu}}{\partial \mathrm{h}} \right)^2 W \mathrm{h}^2 + \left(\frac{\partial \mathrm{Nu}}{\partial \mathrm{L}} \right)^2 W_{\mathrm{L}}^2 + \left(\frac{\partial \mathrm{Nu}}{\partial \mathrm{k}} \right)^2 W \mathrm{k}^2 \right]^{\frac{1}{2}}$$

$$WNu = \left[(0.374)^{2} \cdot (2.09)^{2} + (2395.29)^{2} \cdot (10^{-5})^{2} \right]^{\frac{1}{2}}$$

$$WNu = \pm 0.78$$

$$\frac{W\text{Nu}}{\text{Nu}} = \frac{0.78}{21,55} = 0.036 = 3.6\%$$

For 3.0 W and component 3:

$$k_f = 0.0627 \frac{W}{m k}$$

$$T_{\rm film} = 29.2^{\circ} \text{ C}$$

$$\frac{\partial \text{Nu}}{\partial \text{h}} = \frac{24 \times 10^{-3} \text{m}}{0.0627} = 0.382$$

$$\frac{\partial \text{Nu}}{\partial L} = \frac{135.7}{24 \times 10^{-3}} = 5654.16$$

$$WNu = \left[(0.382)^{2} \cdot (4.92)^{2} + (5654.16)^{2} \cdot (10^{-5})^{2} \right]^{\frac{1}{2}}$$

$$WNu = \pm 1.88$$

$$\frac{W \text{Nu}}{\text{Nu}} = \frac{1.88}{51.94} = 3.62\%$$

$$Ra_f = Gr_f \cdot Pr$$

$$Gr_f = \frac{g\beta L^4 Q_{net}}{k_f v^2 A_{tot}}$$

$$Pr = \frac{v}{\alpha}$$

$$Gr_f = f(g,\beta,L^4,Q_{net},k_f,v^2,A_{tot})$$

Consider fluid properties without uncertainties.

$$\frac{\partial Gr_f}{\partial L^4} = \frac{g\beta Q_{net}}{k_f v^2 A_{tot}}$$

$$\frac{\partial Gr_f}{\partial Q_{net}} = \frac{g\beta L^4}{k_f v^2 A_{tot}}$$

$$\frac{\partial Gr_f}{\partial A_{tot}} = \frac{g\beta L^4 Q_{net}}{k_f v^2 A_{tot}^2}$$

For 0.1 W and component 3:

$$\beta = 0.00137 \text{ K}^{-1}$$

$$k_f = 0.064 \frac{W}{m.k}$$

$$v = 1.11259E-6\frac{m^2}{s}$$

$$\frac{\partial Gr_f}{\partial L^4} = 2.94E13$$

$$\frac{\partial Gr_f}{\partial Q_{net}} = 9.76E7$$

$$\frac{\partial Gr_f}{\partial A_{tot}} = -1.69E10$$

$$W\mathrm{Gr}_{\mathrm{f}} = \left[\left(\frac{\partial \mathrm{Gr}_{\mathrm{f}}}{\partial L^{4}} \right)^{2} W^{2} L^{4} + \left(\frac{\partial \mathrm{Gr}_{\mathrm{f}}}{\partial Q_{\mathrm{net}}} \right)^{2} W^{2} Q_{\mathrm{net}} + \left(\frac{\partial \mathrm{Gr}_{\mathrm{f}}}{\partial A_{\mathrm{tot}}} \right)^{2} W A_{\mathrm{tot}} \right]^{\frac{1}{2}}$$

$$WGr_{f} = \left[(2.94E13)^{2} \cdot (5.5 E-10)^{2} + (9.76E7)^{2} \cdot (0.0025)^{2} \right]^{\frac{1}{2}}$$

+ $(1.69E10)^{2} \cdot (4.8 E-7)^{2}$

$$WGr_f = [2.6E8 + 5.9536E10 + 6.5E7]^{\frac{1}{2}}$$

$$W_{Gr_f} = \pm 243569$$

$$\frac{W_{\rm Gr_f}}{\rm Gr_f} = \frac{243569}{9.67E6} = 2.5\%$$

$$W_{\text{Raf}} = 2.5\%$$

For 3.0 W and component 3:

$$\beta = 0.014 \text{ K}^{-1}$$

$$v = 0.80402 \times 10^{-6} \frac{m^2}{s}$$

$$k_{\rm f}=0.0627\,\frac{\rm W}{\rm m.K}$$

$$\frac{\partial Gr_f}{\partial L^4} = 17.6E15$$

$$\frac{\partial Gr_f}{\partial Q_{net}} = 19.5E7$$

$$\frac{\partial \text{Gr}_{\text{f}}}{\partial \text{A}_{\text{tot}}} = 1.0\text{E}12$$

$$WGr_{f} = \left[\left(17.6 \pm 15\right)^{2} \cdot \left(5.5 \pm -10\right)^{2} + \left(19.5 \pm 7\right)^{2} \cdot \left(0.0742\right)^{2} + \left(1.0 \pm 12\right)^{2} \cdot \left(4.8 \pm -7\right)^{2} \right]^{\frac{1}{2}}$$

$$WGr_f = [9.3E13 + 2.09E14 + 2.38E11]^{\frac{1}{2}}$$

$$\frac{WGr_f}{Gr_f} = \frac{17405183}{584920180} = 2.9\%$$

$$W_{Raf} = 2.9\%$$

APPENDIX C

TABLES

TABLE 1

TEMPERATURE DATA FOR INPUT POWER 0.1 W BOTTOM BOUNDARY AT 20° C

RESULTS ARE STORED IN FILE: 08021455

AMRIENT TEMP: 24.3 C VOLTMETER READING: 1.025 V HEAT EXCHANGER TEMP:: 10-20 C

ALL TEMPERATURES ARE IN DEGREES CELCIUS

	CENTER	TOP	RIGHT	LEFT	BOTTOM	BACK
	17.46E+00 (WATTS):	17.48E+00 10.01E-02	17.48E+00	17.47E+00	17.54E+00	18.04E+00
	17.40E+00 (WATTS):	17.44E+00 10.00E-02	17.47E+00	17.41E+00	17.47E+00	17.96E+00
CHIP NOGE POWER	17+13E+00 (WATTS):	17.08E+00 99.84E-03	17.16E+00	17.22E+00	17.29E+00	17.61E+00
	17.57E+00 (WATTS):	17.56E+00 98.84E-03	17.44E+00	15.60E+00	17.48E+00	17.89E+00
	17.48E+00 (WATTS):	17.62E+00 99.24E-03	17.56E+00	17.51E+00	17.58E+00	17.92E+00
	22.68E+00 (WATTS):	17.39E+00 99.12E-03	17.43E+00	17.38E+00	17.55E+00	18.42E+00
	17.59E+00 (WATTS):	17.62E+00 10.04E-02	17.60E+00	17.55E+00	17.74E+00	18.32E+00
	17.58E+00 (WATTS):	17.64E+00 10.07E-02	17.67E+00	17.58E+00	17.60E+00	18.47E+00
	17.33E+00 (WATTS);	17.15E+00 99.32E-03	17.34E+00	17.30E+00	17.36E+00	17.82E+00

AVERAGE HEAT EXCHANGERS TEMPERATURES:
BOTTOM: 10.01E+00
TOP: 19.97E+00

BACK PLANE TEMPERATURES ARE :

T(55): 17.81E+00 T(56): 18.09E+00 T(57): 17.54E+00 T(72): 18.33E+00 T(73): 18.43E+00 T(74): 18.91E+00 T(75): 18.07E+00 T(75): 18.40E+00 T(77): 18.29E+00

TEMPERATURE DATA FOR INPUT POWER 0.7 W BOTTOM BOUNDARY AT 20° C

RESULTS ARE STORED IN FILE: 08021717

AMBIENT TEMP: 24.4 C VOLTMETER READING: 3.218 V HEAT EXCHANGER TEMP.: 10-20 C

ALL TEMPERATURES ARE IN DEGREES CELCIUS

	CENTER	TOP	RIGHT	LEFT	BOTTOM	BACK
	24.74E+00 (WATTS):	24.02E+00 70.97E-02	23.96E+00	24.00E+00	24.09E+00	27.01E+00
	24.71E+00 (WATTS):	23.81E+00 70.93E-02	23.96E+00	23.54E+00	23.80E+00	26.56E+00
	23.83E+00 (WATTS):	23.69E+00 70.79E-02	23.59E+00	23.55E+00	23.60E+00	25.11E÷00
	24.30E+00 (WATTS):	23.71E+00 70.09E-02	23.60E+00	20.65E+00	23.60E+00	25.74E+00
	24.26E+00 (WATTS):	23.46E+00 70.38E-02	23.44E+00	23.37E+00	23.69E+00	25.46E+00
	26.78E+00 (WATTS):	24.05E+00 70.26E-02	23.44E+00	23.51E+00	24.08E+00	27.57E+00
	24.96E+00 (WATTS):	24.47E+00 71.19E-02	24.02E+00	23.81E+00	24.14E+00	27.58E+00
CHIP NO8: POWER	24.27E+00 (WATTS):	24.14E+00 71.40E-02	24.07E+00	23.85E+00	23.79E+00	29.43E+00
CHIP NO9: FOWER	23.90E+00 (WATTS):	23.70E+00 70.84E-02	23.62E+00	23.50E+00	23.44E+00	26.70E+00

AVERAGE HEAT EXCHANGERS TEMPERATURES:
BOTTOM: 10.00E+00
TOP: 20.00E+00

BACK PLANE TEMPERATURES ARE :

T(55): 20.83E+00 T(56): 21.22E+00 T(57): 20.72E+00 T(72): 21.38E+00 T(73): 21.10E+00 T(74): 21.50E+00 T(75): 21.03E+00 T(76): 21.13E+00 T(77): 21.23E+00

TEMPERATURE DATA FOR INPUT POWER 1.5 W BOTTOM BOUNDARY AT 20° C

RESULTS ARE STORED IN FILE: 08030205

AMBIENT TEMP: 24.4 C VOLTMETER READING: 4.7082 V HEAT EXCHANGER TEMP:: 10-20 C

ALL TEMPERATURES ARE IN DEGREES CELCIUS

	CENTER	TOP	RIGHT	LEFT	BOTTOM	BACK
	33.28E+00 (WATTS):	31.29E+00 15.17E-01	31.67E+00	31.63E+00	31.81E+00	37.53E+00
	33.22E+00 (WATTS):	31.21E+00 15.16E-01	31.50E+00	30.68E+00	31.25E+00	36.83E+00
	31.23E+00 (WATTS):	31.26E+00 15.13E-01	30.99E+00	30.76E+00	30.63E+00	34.16E+00
	33.06E+00 (WATTS):	31.52E+00 14.98E-01	31.54E+00	27.88E+00	31.60E+00	35.83E+00
	32.56E+00 (WATTS):	30.25E+00 15.04E-01	30.60E+00	30.44E+00	31.30E+00	34.65E+00
	20.87E+00 (WATTS):	32.79E+00 15.01E-01	30.75E+00	31.13E+00	32.43E+00	43.50E+00
POWER	33.79E+00 (WATTS):	32.54E+00 15.21E-01	31.83E+00	31.29E+00	31.97E+00	38.83E+00
	32.46E+00 (WATTS):	31.64E+00 15.26E-01	31.72E+00	31.46E+00	31.25E+00	43.11E+00
	31.47E+00 (WATTS):	31.25E+00 15.14E-01	31.12E+00	30.80E+00	31.01E+00	37.41E+00

AVERAGE HEAT EXCHANGERS TEMPERATURES:
BOTTOM: 10.09E+00
TOP: 20.04E+00

BACK PLANE TEMPERATURES ARE :

T(55): 23.97E+00 T(56): 24.51E+00 T(57): 25.05E+00 T(72): 24.93E+00 T(73): 24.57E+00 T(74): 24.85E+00 T(75): 25.10E+00 T(77): 24.49E+00 T(77): 24.61E+00

TEMPERATURE DATA FOR INPUT POWER 3.0 W BOTTOM BOUNDARY AT 20° C

RESULTS ARE STORED IN FILE: 00041705

AMBIENT TEMP: 24.5 C VOLTMETER READING: 6.601 V HEAT EXCHANGER TEMP.: 10-20 C

ALL TEMPERATURES ARE IN DEGREES CELCIUS

	CENTER	TOP	RIGHT	LEFT	BOTTOM	BACK
CHIP NO1: POWER	49.47E+00 (WATTS):	45.65E+00 29.74E-01	46.44E+00	46.13E+00	45.76E+00	56.26E+00
CHIP NO2: POWER	48.99E+00 (WATTS):	45.37E+00 29.73E-01	46.33E+00	44.51E+00	46.02E+00	56.02E+00
CHIP NO3: POWER	44.62E+00 (WATTS):	45.57E+00 29.68E-01	45.04E+00	44.58E+00	44.60E+00	51.20E+00
	49.59E+00 (WATTS):	46.17E+00 29.38E-01	46.77E+00	42.62E+00	46.97E+00	54.89E+00
CHIP NOS: POWER	48.69E+00 (HATTS):	43.92E+00 29.51E-01	45.19E+00	44.75E+00	46.43E+00	52.53E+00
CHIP NO6: POWER	37.80E+00 (WATTS):	48.64E+00 29.40E-01	45.04E+00	45.78E+00	47.85E+00	68.62E+00
	51.18E+00 (WATTS):	48.27E+00 29.82E-01	47.48E+00	46.51E+00	47.28E+00	58.60E+00
CHIP NO8: POWER	48.09E+00 (WATTS);	47.05E+00 29.91E-01	47.09E+00	46.58E+00	45.99E+00	67.94E+00
CHIP NO9: POWER	44.97E+00 (WATTS):	45.78E+00 29.69E-01	45.57E+00	45.11E+00	44.78E+00	58.25E+00

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AVERAGE HEAT EXCHANGERS TEMPERATURES:
BOTTOM: 10.98E+00
TOP: 20.08E+00

BACK PLANE TEMPERATURES ARE :

1(55): 31.46E+00 1(56): 32.62E+00 1(57): 34.30E+00 1(72): 33.38E+00 1(73): 32.78E+00 1(74): 33.27E+00 1(75): 33.99E+00 1(77): 32.42E+00

REDUCED DATA FOR INPUT POWER 0.1 W BOTTOM BOUNDARY AT 20° C

THE RAN Emf DATA ARE FROM THE FILE: 08021455 THE POWER SETTING PER CHIP WAS: 0.1 W

	THE PONER	SETTING PER CHIP	WAS: 0.1 W	, 1435
CHIP	QNET(W)	Tavg-Is	Nu	ZUNC IN Nu
1	99.93E-03 TEMPERATURE BASED RAY % UNCERTAINTY IN THE FLUX BASED RAYLEIGH N % UNCERTAINTY IN FLUX	'LEIGH NUMBER * E-7 TEMPERATURE BASED JUMBER * E-8 IS: 4	7 IS: 139.72E RAYLEIGH NUME 106.58E-04	-03 BER IS :134.16E-02
2	99.84E-03 TEMPERATURE BASED RAY % UNCERTAINTY IN THE FLUX BASED RAYLEIGH N % UNCERTAINTY IN FLUX	LEIGH NUMBER * E-7 TEMPERATURE BASED JUMBER * E-8 IS: 4	7 IS: 138.74E RAYLEIGH NUME ₹05.97E-04	-03 ER IS :135.03E-02
3	99.64E-03 TEMPERATURE BASED RAY % UNCERTAINTY IN THE FLUX BASED RAYLEIGH N % UNCERTAINTY IN FLUX	LEIGH NUMBER + E-7 TEMPERATURE BASED NUMBER + E-8 IS: 4	' IS: 133.57E RAYLEIGH NUME 103.97E-04	-03 ER IS :139.86E-02
4	98.64E-03 7 TEMPERATURE BASED RAY % UNCERTAINTY IN THE FLUX BASED RAYLEIGH N % UNCERTAINTY IN FLUX	LEIGH NUMBER * E-7 TEMPERATURE BASED UMBER * E-8 IS: 3	' IS: 130.83E RAYLEIGH NUMB 899.28E-04	-03 ER IS :142.58E-02
5	99.04c-03 7	5.15E-01 28.	64E-01	13.32E-01

- 5 99.04-03 75.15E-01 28.64E-01 13.32E-01
 TEMPERATURE BASED RAYLEIGH NUMBER + E-7 IS: 140.78E-03
 % UNCERTAINTY IN THE TEMPERATURE BASED RAYLEIGH NUMBER IS: :133.23E-02
 FLUX BASED RAYLEIGH NUMBER E-8 IS: 403.22E-04
 % UNCERTAINTY IN FLUX BASED RAYLEIGH NUMBER IS: 462.64E-05
- 6 98.92E-03 91.61E-01 23.49E-01 10.93E-01
 TEMPERATURE BASED RAYLEIGH NUMBER * E-7 IS: 174.75E-03
 % UNCERTAINTY IN THE TEMPERATURE BASED RAYLEIGH NUMBER IS: 103.29E-02
 FLUX BASED RAYLEIGH NUMBER * E-8 IS: 410.50E-04
 % UNCERTAINTY IN FLUX BASED RAYLEIGH NUMBER IS: 463.23E-05
- 7 10.02E-02 75.85E-01 28.72E-01 12:20E-01
 IEHPERATURE BASED RAYLEIGH NUMBER * E-7 IS: 142.13E-03
 % UNCERTAINTY IN THE TEMPERATURE BASED RAYLEIGH NUMBER IS: 132.01E-02
 FLUX BASED RAYLEIGH NUMBER * E-8 IS: 408.40E-04
 % UNCERTAINTY IN FLUX BASED RAYLEIGH NUMBER IS: 457.14E-05
- 8 10.05E-02 75.98E-01 28.75E-01 13.18E-01 TEMPERATURE BASED RAYLEIGH NUMBER * E-7 IS: 142.45E-03 % UNCERTAINTY IN THE TEMPERATURE BASED RAYLEIGH NUMBER IS::131.78E-02 FLUX BASED RAYLEIGH NUMBER * E-8 IS: 409.59E-04 % UNCERTAINTY IN FLUX BASED RAYLEIGH NUMBER IS: 455.89E-05
- 9 99.72E-03 73.00E-01 29.68E-01 13.72E-01 EMPERATURE BASED RAYLEIGH NUMBER * E-7 IS: 136.42E-03 % UNCERTAINTY IN THE TEMPERATURE BASED RAYLEIGH NUMBER IS: :137.15E-02 FLUX BASED RAYLEIGH NUMBER * E-8 IS: 404.34E-04 % UNCERTAINTY IN FLUX BASED RAYLEIGH NUMBER IS: 459.52E-05

REDUCED DATA FOR INPUT POWER 0.7~WBOTTOM BOUNDARY AT $20^{\circ}~C$

THE RAW Emf DATA ARE FROM THE FILE: 08021717
THE POWER SETTING PER CHIP WAS: 0.7 WATTS

	*****	· onen oer ino i en	01121 111101 011		
CHIP	QNET(W)	Tavg-Ts	Nu	XUNC IN Nu	,
1	% UNCERTAINTY IN FLUX BASED RAYLE	D RAYLEIGH NUMBER	* E-7 IS: 297 ASED RAYLEIGH I S: 308.85E-03	.08E-03 NUMBER IS :703.04E-03	
2	TEMPERATURE BASE % UNCERTAINTY IN FLUX BASED RAYLE	14.08E+00 D RAYLEIGH NUMBER THE TEMPERATURE B IGH NUMBER * E-8 I FLUX BASED RAYLEI	* E-7 IS: 283 ASED RAYLEIGH M S: 308.10E-03	.28E-03 HUMBER IS :711.21E-03	
3	% UNCERTAINTY IN FLUX BASED RAYLE	D RAYLEIGH NUMBER	+ E-7 IS: 273. ASED RAYLEIGH N S: 306.03E-03	.69E-03 NUMBER IS :732.84E-03	
4	% UNCERTAINTY IN FLUX BASED RAYLE	D RAYLEIGH NUMBER	* E-7 IS: 260. ASED RAYLEIGH N S: 301.00E-03	.80E-03 NUMBER IS :764.36E-03	
	TEMPERATURE BASE % UNCERTAINTY IN FLUX BASED RAYLE	13.71E+00 D RAYLEIGH NUMBER THE TEMPERATURE B IGH NUMBER * E-8 I' FLUX BASED RAYLEI	* E-7 IS: 274. ASED RAYLEIGH M S: 304.37E-03	81E-03 NUMBER IS :730.23E-03	
	TEMPERATURE BASE % UNCERTAINTY IN FLUX BASED RAYLE	14.67E+00 D RAYLEIGH NUMBER THE TEMPERATURE BO IGH NUMBER * E-8 IN FLUX BASED RAYLEIG	* E-7 IS: 297. ASED RAYLEIGH M S: 307.22F-03	.03E-03 NUMBER IS :682.63E-03	
	TEMPERATURE BASE % UNCERTAINTY IN FLUX BASED RAYLE	14.32E+00 D RAYLEIGH NUMBER THE TEMPERATURE BI IGH NUMBER + E-8 IS FLUX BASED RAYLEI	+ E-7 IS: 288. ASED RAYLEIGH N S: 310.07E-03	95E-03 NUMBER IS :699.10E-03	
	TEMPERATURE BASE % UNCERTAINTY IN FLUX BASED RAYLE	14.06E+00 D RAYLEIGH NUMBER THE TEMPERATURE BA IGH NUMBER * E-8 IS FLUX BASED RAYLEIG	* E-7 IS: 282. ASED RAYLEIGH N 5: 310.07E-03	84E-03 NUMBER IS :712.17E-03	
	TEMPERATURE BASE % UNCERTAINTY IN FLUX BASED RAYLE	13.67E+00 D RAYLEIGH NUMBER 3 THE TEMPERATURE BA IGH NUMBER * E-8 IS FLUX BASED RAYLEIG	F-7 IS: 273. ASED RAYLEIGH N S: 306.28E-03	90E-03 HUMBER IS :732.34E-03	

REDUCED DATA FOR INPUT POWER 1.5 W BOTTOM BOUNDARY AT 20° C

THE RAW Emf DATA ARE FROM THE FILE: 08030205 THE POWER SETTING PER CHIP WAS: 1.5 WATTS

CHIP	ONET(H)	Tavg-Ts	Nu	%UNC IN Nu
1	" UNCERTAINTY I FLUX BASED RAYL	22.08E+00 ED RAYLEIGH NUMBER N THE TEMPERATURE E EIGH NUMBER * E-8 I N FLUX BASED RAYLEI	* E-7 IS: 48 BASED RAYLEIGH S: 722.22E-0	4.85E-03 NUMBER IS :453.37E-03 3
2	TEMPERATURE BAS % UNCERTAINTY IN FLUX BASED RAYL	21.73E+00 ED RAYLEIGH NUMBER N THE TEMPERATURE B EIGH NUMBER * E-8 I N FLUX BASED RAYLEI	+ E-7 IS: 479 BASED RAYLEIGH IS: 719.11E-03	5.36E-03 NUMBER IS :460.71E-03 3
3	TEMPERATURE BASE % UNCERTAINTY IN FLUX BASED RAYLO	20.92E+00 ED RAYLEIGH NUMBER N THE TEMPERATURE B EIGH NUMBER → E-8 I N FLUX BASED RAYLEI	* E-7 IS: 450 BASED RAYLEIGH S: 711.25E-00	3.60E-03 NUMBER IS :478.68E-03
	TEMPERATURE BASI % UNCERTAINTY IN FLUX BASED RAYLI	21.04E+00 ED RAYLEIGH NUMBER N THE TEMPERATURE B EIGH NUMBER * E-8 I N FLUX BASED RAYLEI	* E-7 IS: 45 ASED RAYLEIGH S: 705.05E-03	7.00E-03 NUMBER IS :475.76E-03
	TEMPERATURE BASE % UNCERTAINTY IN FLUX BASED RAYLE	21.15E+00 ED RAYLEIGH NUMBER N THE TEMPERATURE B EIGH NUMBER → E-8 I N FLUX BASED RAYLEI	* E-7 IS: 459 ASED RAYLEIGH S: 708.81E-03	9.81E-03 NUMBER IS :473.39E-03
	TEMPERATURE BASI % UNCERTAINTY IN FLUX BASED RAYLE	17.77E+00 ED RAYLEIGH NUMBER N THE TEMPERATURE B EIGH NUMBER * E-8 I N FLUX BASED RAYLEI	* E-7 IS: 372 ASED RAYLEIGH S: 680.72E-03	2.79E-03 NUMBER IS :563.37E-03

- 7 15.04E-01 22.33E-00 14.78E-00 44.90E-02 TEMPERTURE BASED RAYLEIGH NUMBER * E-7 IS: 491.49E-03 % UNCERTAINTY IN THE TEMPERATURE BASED RAYLEIGH NUMBER IS: 448.39E-03 FLUX BASED RAYLEIGH NUMBER * E-8 IS: 726.23E-03 % UNCERTAINTY IN FLUX BASED RAYLEIGH NUMBER IS: 224.56E-04
- 8 15.09E-01 21.76E+00 15.20E+00 46.06E-02
 IEHPERATURE BASED RAYLEIGH NUMBER + E-7 15: 476.17E-03
 % UNCERTAINTY IN THE TEMPERATURE BASED RAYLEIGH NUMBER IS: 460.08E-03
 FLUX BASED RAYLEIGH NUMBER + E-8 IS: 723.92E-03
 % UNCERTAINTY IN FLUX BASED RAYLEIGH NUMBER IS: 223.86E-04
- 9 14.97E-01 21.07E+00 15.58E+00 47.58E-02 **TEMPERATURE BASED RAYLEIGH NUMBER + E-7 IS: 457.63E-03 **Z UNCERTAINTY IN THE TEMPERATURE BASED RAYLEIGH NUMBER IS: 475.23E-03 **FLUX BASED RAYLEIGH NUMBER + E-8 IS: 712.92E-03 **Z UNCERTAINTY IN FLUX BASED RAYLEIGH NUMBER IS: 225.59E-04

REDUCED DATA FOR INPUT POWER 3.0 W BOTTOM BOUNDARY AT 20° C

THE ROW Em (DATA ARE FROM THE FILE: 08041705

	1176	THE POWER SETTING	PER CHIP WAS: 3.	0 WATTS
.H.P	QNET (W	Tavg-Ts	Nu	ZUNC IM Nu
1	TEMPERATURE % UNCERTAIN FLUX BASED F	BASED RAYLEIGH NUM TY IN THE TEMPERATI RAYLEIGH NUMBER * B	17.97E+00 MBER * E-7 IS: 936 URE BASED RAYLEIGH E-B IS: 168.28E-02 AYLEIGH NUMBER IS:	.63E-03 NUMBER IS :276.00E-03
2	% UNCERTAINT	BASED RAYLEIGH NUM FY IN THE TEMPERATU RAYLEIGH NUMBER * 1	18.25E+00 MBER * E-7 IS: 915 URE BASED RAYLEIGH E-8 IS: 167.20E-02 AYLEIGH NUMBER IS:	.94E-03 NUMBER IS :280.60E-03
3	TEMPERATURE % UNCERTAIN FLUX BASED F	BASED RAYLEIGH NUM TY IN THE TEMPERATU RAYLEIGH NUMBER * E	19.20E+00 MBER * E-7 IS: 852 URE BASED RAYLEIGH E-8 IS: 163.66E-02 AYLEIGH NUMBER IS:	.2BE-03 NUMBER IS :296.05E-03
4	TEMPERATURE % UNCERTAINT FLUX BASED F	BASED RAYLEIGH NUM Y IN THE TEMPERATU RAYLEIGH NUMBER * E	18.05E+00 HBER * E-7 IS: 915 URE BASED RAYLEIGH E-8 IS: 165.19E-02 AYLEIGH NUMBER IS:	.27E-03 NUMBER IS :2B0.75E-03
5	TEMPERATURE % UNCERTAINT FLUX BASED F	BASED RAYLEIGH MUN Y IN THE TEMPERATU RAYLEIGH NUMBER * E	18.32E+00 1BER * E-7 IS: 901 URE BASED RAYLEIGH E-8 IS: 165.19E-02 AYLEIGH NUMBER IS:	.62E-03 NUMBER IS :283.B9E-03
6	% UNCERTAINT FLUX BASED F	BASED RAYLEIGH NUM Y IN THE TEMPERATU RAYLEIGH NUMBER * E	19.85E+00 HBER * E-7 IS: 804 URE BASED RAYLEIGH E-8 IS: 159.62E-02 HYLEIGH NUMBER IS:	.05E-03 NUMBER IS :309.31E-03
	% UNCERTAINT FLUX BASED R	BASED RAYLEIGH NUM Y IN THE TEMPERATU AYLEIGH NUMBER * E	17.42E+00 MBER * E-7 IS: 981 URE BASED RAYLEIGH L-8 IS: 170.99E-02 AYLEIGH NUMBER IS:	.44E-03 NUMBER [*] IS :266.69E-03
	% UNCERTAINT FLUX BASED F	BASED RAYLEIGH NUM Y IN THE TEMPERATU RAYLEIGH NUMBER * E	18.09E+00 MBER * E-7 IS: 934 MRE BASED RAYLEIGH E-8 IS: 169.15E-02 YLEIGH NUMBER IS:	.88E-03 NUMBER IS :276.38E-03
9	% UNCERTAINT FLUX BASED R	BASED RAYLEIGH NUM Y IN THE TEMPERATU AYLEIGH NUMBER * E	18.9BE+00 BBER * E-7 IS: 866 IRE BASED RAYLEIGH 1-8 IS: 164.42E-02 BYLEIGH NUMBER IS:	.10E-03 NUMBER IS :292.51E-03

TEMPERATURE DATA FOR INPUT POWER 0.1 W BOTTOM BOUNDARY INSULATED

THESE RESULTS ARE STORED IN FILE: 08221255

AMBIENT TEMP WAS: 23.0 C VOLTMETER READING WAS: 1.2134 V BATH TEMP WAS: 10 C-INSUL

ALL TEMPERATURES ARE IN DEGREES CELCIUS

	CENTER	TOP	RIGHT	LEFT	BOTTOM	BACK
CHIP 101: POWER	15.92E+00 (HATTS):	15.85E+00 10.08E-02	15.85E+00	15.82E+00	15.87E+00	16.36E+00
CHIP NO2: POWER	15.32E+00 (WATTS):	15.95E+00 10.07E-02	15.98E+00	15.87E+00	15.95E+00	16.44E+00
CHIP NO3: POWER	15.7 E+00 [WATTS]:	15.66E+00 10.05E-02	15.78E+00	15.82E+00	15.86E+00	16.14E+00
CHIP NO4: POWER	15.77E+00 WATTS1:	15.93E+00 99.49E-03	15.72E+00	15.64E+00	15.71E+00	16.12E+00
CHIP WOS: POWER	15.77E+00 WATTS1:	15.87E+00 93.89E-03	15.84E+00	15.77E+00	15.85E+00	16.20E+00
CHIP NOS: POWER	17.93E+00 (WATTST:	15.73E+00 99.74E-03	15.77E+00	15.71E+00	12.78E+00	16.59E+00
C P NO7: POHER		15.79E+00 10.11E-02	15.75E+00	15.71E+00	15.84E+00	16.4/E+00
CHIP NO8:	15.85E+00 WATTS1:	15.36E-00 10.14E-02	15.91E+00	15.82E+00	15.83E+00	16.56E+00
CHIP HOS:	15.56E+00 [WATTS]:	15.49E+00 10.05E-02	15.625+00	15.59E+00	15.64E+00	16.15E+00

HEAT EICHANGERS TEMPERATURES: BOTTOM: TOP:

RIGHT LEFT 15.97E+00 15.97E+00 10.20E+00 96.30E-01

BACK PLANE TEMPERATURES ARE :

T(55): 15.01E-00 T(56): 16.41E-00 T(57): 16.01E-00 T(72): 16.73E+00 T(73): 16.73E+00 T(74): 17.24E+00 T(75): 16.42E+00 T(77): 16.69E+00

TEMPERATURE DATA FOR INPUT POWER 0.7 W BOTTOM BOUNDARY INSULATED

THESE RESULTS ARE STORED IN FILE: 08222257

AMBIENT TEMP WAS: 21.7 C VOLTMETER READING WAS: 3.22 V BATH TEMP WAS: 10 C-INS

ALL TEMPERATURES ARE IN DEGREES CELCIUS

	CENTER	TOP	RIGHT	LEFT	BOTTOM	BACK
	23.67E+00 (WATTS):	22.96E+00 70.88E-02	22.84E+00	22.84E+00	22.85E+00	25.39E+00
CHIP NO2: POWER	23.52E+00 (WATTS):	22.57E+00 70.83E-02	22.76E+00	22.30E+00	22.68E+00	25.39E+00
CHIP NO3: POWER	22.90E+00 (WATTS):	22.62E+00 70.69E-02	22.51E+00	22.47E+00	22.24E+00	24.00E+00
CHIP NO4: POWER	23.46E+00 (WATTS):	22.91E+00 69.99E-02	22.73E+90	22.17E+00	22.67E+00	24.75E+00
CHIP NOS: POWER	23.20E+00 (WATTS):	22.20E+00 70.28E-02	22.27E+00	22.14E+00	22.60E+00	24.21E+00
	26.26E+00 (WATTS):	22.78E+00 70.15E-02	22.23E+00	22.30E+00	18.88E+00	26.38E+00
C *P NO7: POWER	23.85E+00 (WATTS):	23.15E+00 71.09E-02	22.80E+00	22.60E+00	22.93E+00	25.70E+00
CHIP NO8: POWER	23.17E+00 (WATTS):	22.97E+00 71.30E-02	22.85E+00	22.70E+00	22.60E+00	26.66E+00
CHIP NO9: POWER	22.70E+00 (WATTS);	22.48E+00 70.72E-02	22.43E+00	22.26E+00	22.24E+00	25.53E÷00

HEAT	EXCHANGERS BOTTOM: TOP:	TEMPERATURES:
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RIGHT LEFT 17.35E+00 17.36E+00 10.29E+00 97.63E-01

BACK PLANE TEMPERATURES ARE :

T(55): 19.34E+00 T(56): 19.81E+00 T(57): 19.74E+00 T(72): 20.01E+00 T(73): 71.30E-01 T(74): 19.99E+00 T(75): 19.59E+00 T(76): 19.76E+00 T(77): 19.88E+00

TEMPERATURE DATA FOR INPUT POWER 1.1 W BOTTOM BOUNDARY INSULATED

THESE RESULTS ARE STORED IN FILE: 08231010

AMBIENT TEMP WAS: 21.33 C VOLTMETER READING WAS: 4.00 V BATH TEMP WAS: 10 C-INS

ALL TEMPERATURES ARE IN DEGREES CELCIUS

	CENTER	TOP	RIGHT	LEFT	BOTTOM	BACK
	28.35E+00 (WATTS):	26.73E+00 10.96E-01	27.12E+00	27.11E+00	27.13E+00	30.82E+00
	28.16E+00 (WATTS):	26.70E+00 10.95E-01	26.93E+00	26.29E+00	26.90E+00	30.97E+00
	26.96E+00 (WATTS):	26.97E+00 10.93E-01	26.7NE+00	26.57E+00	26.26E+00	28.94E+00
	28.21E+00 (HATTS):	27.02E+00· 10.82E-01	27.14E+00	26.29E+00	27.07E+00	30.17E+00
	27.75E+00 (WATTS):	26.13E+00 10.87E-01	26.25E+00	26.09E+00	26.86E+00	29.20E+00
	27.17E+00 (WATTS):	27.20E+00 10.84E-01	26.33E+00	26.45E+00	25.80E+00	32.61E+00
C' TP NO7: POWER	28.65E+00 (WATTS):	27.60E+00 10.99E-01	27.07E+00	26.77E+00	27.15E+00	31.29E+00
CHIP NO8: POWER	27.65E+00 (WATTS):	26.99E+00 11.02E-01	27.08E+00	26.92E+00	26.57E+00	32.87E+00
CHIP NO9:	26.81E+00	26.65E+00	26.59E+00	26.36E+00	26.23E+00	31.29E+00

HEAT	BOTTOM:	TEMPERATURES
	TOP:	

RIGHT LEFT 18.43E+00 18.43E+00 10.21E+00 97.25E-01 \$

BACK PLANE TEMPERATURES ARE :

1(55):	21.49E+00
T(56):	22.00E+00
T(57):	22.27E+00
T(72):	22.32E+00
T(73):	21.94E+00
T(74):	22.22E+00
T(75):	22.04E+00
T(76):	21.97E+00
T(77):	22.12F+00

TEMPERATURE DATA FOR INPUT POWER 3.0 W BOTTOM BOUNDARY INSULATED

THESE RESULTS ARE STORED IN FILE: 08231310

AMBIENT TEMP WAS: 23 C VOLTHETER READING WAS: 4.00 V BATH TEMP WAS: 10 C-INS

ALL TEMPERATURES ARE IN DEGREES CELCIUS

	CENTER	TOP	RIGHT	LEFT	BOTTOM	BACK
CHIP NO1: POWER	54.28E+00 (WATTS):	49.66E+00 30.12E-01	50.72E+00	50.63E+00	50.34E+00	59.54E+00
CHIP NO2: POWER	53.84E+00 (WATTS):	49.73E+00 30.11E-01	50.52E+00	48.65E+00	50.06E+00	60.06E+00
CHIP NO3: POWER	50.25E+00 (WATTS):	50.25E+00 30.06E-01	49.56E+00	49.03E+00	47.98E+00	55.22E+00
CHIP NO4: POWER	53.66E+00 (WATTS):	49.30E+00- 29.77E-01	50.54E+00	48.37E+00	50.35E+00	58.19E+00
CHIP NOS: POWER	52.76E+00 (WATTS):	47.84E+00 29.89E-01	48.71E+00	48.29E+00	49.81E+00	55.75E+00
CHIP NO6: POWER	55.76E+00 (WATTS):	51.99E+00 29.78E-01	48.65E+00	49.14E+00	50.78E+00	70.28E+00
C TP NOT: POWER	55.44E+00 (WATTS):	51.67E+00 30.21E-01	50.76E+00	50.15E+00	50.57E+00	60.78E+00
	52.46E+00 (WATTS):	51.07E+00 30.30E-01	51.00E+00	50.88E+00	50.31E+00	67.37E+00
	50.77E+00 (WATTS):	50.34E+00 30.06E-01	49.91E+00	49.40E+00	49.60E+00	61.43E+00

HEAT EXCHANGE	RS TEMPERATURES:	RIGHT	LEFT
BOITOM:		21.94E+00	21.96E+00
TOP:		11.02E+00	98.81E-01

BACK PLANE TEMPERATURES ARE :

1(55):	32.74E+00
T(56):	34.26E+00
T(57):	36.45E+00
T(72):	35.41E+00
T(73):	34.76E+00
T(74):	35.18E+00
T(75):	35.96E+00
T(76):	34,28E+00
T(77) +	34 30E+00

REDUCED DATA FOR INPUT POWER 0.1 W BOTTOM BOUNDARY INSULATED

THE RAW Emf DATA ARE FROM THE FILE: 08221255 THE POWER SETTING PER CHIP WAS: 0.1 NATTS

CHIP	GNET (W)	Tavg-Ts	Nu	%UNC IN Nu	
1	10.06E-02 TEMPERATURE BASED % UNCERTAINTY IN FLUX BASED RAYLEI % UNCERTAINTY IN	RAYLEIGH NUMBE THE TEMPERATURE GH NUMBER * E-8	BASED RAYLEIGH N IS: 401.14E-04	69E-03 NUMBER IS :169.28	E - 0
2	10 055-02		36 31F-01		

- 2 10.05E-02 60.09E-01 36.31E-01 16.67E-01 THERERATURE BASED RAYLEIGH NUMBER * E-7 IS: 110.46E-03 2 UNCERTAINTY IN THE TEMPERATURE BASED RAYLEIGH NUMBER IS: 166.74E-02 FLUX BASED RAYLEIGH NUMBER * E-8 IS: 401.11E-04 2 UNCERTAINTY IN FLUX BASED RAYLEIGH NUMBER IS: 394.58E-05
- 3 10.03E-02 \$3.46E-01 37.26E-01 17.14E-01 TEHPERATURE BASED PAYLEIGH NUMBER *E-7 IS: 107.28E-03 2 UNKERTATURT IN THE TEMPERATURE BASED RAYLEIGH NUMBER IS:171.38E-02 FLUX BASED RAYLEIGH NUMBER *E-8 IS: 399.54E-04 2 UNKERTATURT NA FLUX BASED RAYLEIGH NUMBER IS: 395.38E-05
- 4 99,32E-03 53.11E-01 37.11E-01 17.24E-01
 TEMPERATURE BASED RAYLEIGH NUMBER + E-7 IS: 106.58E-03
 % UNCERTAINT! IN THE TEMPERATURE BASED RAYLEIGH NUMBER IS:172.43E-02
 FLUX BASED RAYLEIGH NUMBER + E-8 IS: 395.51E-04
 % UNCERTAINT! IN FLUX BASED RAYLEIGH NUMBER IS: 399.24E-05
- 5 99,73E-03 \$9,80E-01 36,79E-01 17.03E-01 IEHPERATURE BASED RAYLEIGH NUMBER + E-7 IS: 108.02E-03 % UNCERTAINTY IN THE TEMPERATURE BASED RAYLEIGH NUMBER IS: 170.27E-02 FLUX BASED RAYLEIGH NUMBER + E-8 IS: 397.44E-04 % UNCERTAINTY IN FLUX BASED RAYLEIGH NUMBER IS: 397.65E-05
- 6 99.58E-03 53.05E-01 34.29E-01 15.89E-01
 TEHPERATURE BASED RAYLEIGH NUHBER * E-7 IS: 116.29E-03
 Z UNCERTAINTY IN THE TEMPERATURE BASED RAYLEIGH NUMBER IS: 158.90E-02
 FLUX BASED RAYLEIGH NUMBER * E-8 IS: 398.81E-04
 X UNCERTAINTY IN FLUX BASES RAYLEIGH NUMBER IS: 398.24E-05
- 7 10.09E-02 58.34E-01 37.56E-01 17.17E-01 IEHFERATURE BASED RAYLEIGH NUHBER + E-7 IS: 107.04E-03 % UNCERTAINT! IN THE TEMFERATURE BASED RAYLEIGH NUMBER IS: 171.73E-02 FLUX BASED RAYLEIGH NUMBER + E-8 IS: 402.00E-04 % UNCERTAINTY IN FLUX BASED RAYLEIGH NUMBER IS: 392.90E-05
- 8 10,12E-02 \$9.41E-01 36.98E-01 16.87E-01
 TEMPERATURE BASED RAYLEIGH NUMBER * E-7 IS: 109.12E-03
 % UNCERTAINTY IN THE TEMPERATURE BASED RAYLEIGH NUMBER IS: :168.66E-02
 FLUX BASED RAYLEIGH NUMBER * E-8 IS: 403.56E-04
 % UNCERTAINTY IN FLUX BASED RAYLEIGH NUMBER IS: 391.87E-05
- 9 10.04E-02 55.68E-01 38.43E-01 17.68E-01 1EMPERATURE BASED RAYLEIGH NUMBER # E-7 IS: 103.80E-03 2 UNCERTAINTY IN THE TEMPERATURE BASED RAYLEIGH NUMBER IS:176.77E-02 FLUX BASED RAYLEIGH NUMBER # E-8 IS: 398.9SE-04 2 UNCERTAINTY IN FLUX BASED RAYLEIGH NUMBER IS: 395.13E-05

REDUCED DATA FOR INPUT POWER 0.7 W BOTTOM BOUNDARY INSULATED

THE RAN Emf DATA ARE FROM THE FILE: 08222257
THE POWER SETTING PER CHIP WAS: 0.7 WATTS

CHIP	QNET(W)	Tavg-Ts	Nu	ZUNC IN Nu
1	70.13E-02 TEMPERATURE BASED % UNCERTAINTY IN 1 FLUX BASED RAYLEIG % UNCERTAINTY IN F	HE TEMPERATURE BA H NUMBER * E-8 IS	ASED RAYLEIGH I S: 304.66E-03	NUMBER IS :764.35E-0
2	TEMPERATURE BASED	HE TEMPERATURE BA	* E-7 IS: 255 ASED RAYLEIGH N 5: 303.54E-03	.36E-03 NUMBER IS :779.20E-0
3	69.94E-02 TEMPERATURE BASED % UNCERTAINTY IN T FLUX BASED RAYLEIG % UNCERTAINTY IN F	HE TEMPERATURE BA H NUMBER → E-8 IS	SED RAYLFIGH I	NUMBER IS :795.34E-0
4	TEMPERATURE BASED	HE TEMPERATURE BE H NUMBER * E-8 IS	E-7 IS: 254 SED RAYLEIGH N : 299.83F-03	.59E-03 NUMBER IS :781.28E-0
5	69.53E-02 TEMPERATURE BASED % UNCERTAINTY IN T FLUX BASED RAYLEIG % UNCERTAINTY IN F	HE TEMPERATURE BA H NUMBER * F-8 IS	SED RAYLEIGH 1	NUMBER IS :798.47E-0
6	TEMPERATURE BASED	HE TEMPERATURE BA H NUMBER * E-8 IS	E-7 IS: 266 SED RAYLEIGH N : 302.30E-03	.31E-03 NUMBER IS :751.07E-0
7	TEMPERATURE BASED	HE TEMPERATURE BA H NUMBER * E-8 IS	E-7 IS: 261. ISED RAYLEIGH N : 305.62E-03	31E-03 NUMBER IS :763.62E-0
8	70.55E-02 TEMPERATURE BASED % UNCERTAINTY IN T FLUX BASED RAYLEIG % UNCERTAINTY IN F	HE TEMPERATURE BA H NUMBER * E-8 IS	SED RAYLEIGH N : 305.69E-03	UMBER IS :777.86E-03
9	69.97E-02 TEMPERATURE BASED % UNCERTAINTY IN T FLUX BASED RAYLEIG % UNCERTAINTY IN F	HE TEMPERATURE BA H NUMBER * E-8 IS	E-7 IS: 246. SED RAYLEIGH N : 301.64E-03	04E-03 NUMBER IS :805.10E-03

REDUCED DATA FOR INPUT POWER 1.1 W BOTTOM BOUNDARY INSULATED

THE RAW Emf DATA ARE FROM THE FILE: 08231010
THE POWER SETTING PER CHIP WAS: 1.1 WATTS

CHIP	DUF L (M)	Tavg-Ts	Nu	ZUNC IN Nu	
1	% UNCERTAINTY IN FLUX BASED RAYLE	17.53E+00 D RAYLEIGH NUMBER THE TEMPERATURE I IGH NUMBER * E-9 FLUX BASED RAYLE	BASED RAYLEIGH IS: 494.53E-03	NUMBER IS :571.25E-03	
2	TEMPERATURE BASE % UNCERTAINTY IN FLUX BASED RAYLE	17.19E+00 D RAYLEIGH NUMBER THE TEMPERATURE E IGH NUMBER * E-8 FLUX BASED RAYLEI	* E-7 IS: 357 BASED RAYLEIGH IS: 492.30E-03	7.49E-03 NUMBER IS :582.43E-03	
3	TEMPERATURE BASE % UNCERTAINTY IN FLUX BASED RAYLE	16.77E+00 D RAYLEIGH NUMBER THE TEMPERATURE I IGH NUMBER * E-8 I FLUX BASED RAYLE:	* E-7 IS: 347 BASED RAYLEIGH IS: 489.01E-03	7.17E-03 NUMBER IS :597.04E-03	
4	TEMPERATURE BASE % UNCERTAINTY IN FLUX BASED RAYLE	17.30E+00 D RAYLEIGH NUMBER THE TEMPERATURE E IGH NUMBER * E-8 I FLUX BASED RAYLEI	* E-7 IS: 360 BASED RAYLEIGH IS: 487.09E-03	0.14E-03 NUMBER IS :578.80E-03	
5	TEMPERATURE BASE % UNCERTAINTY IN FLUX BASED RAYLE	16.78E+00 D RAYLEIGH NUMBER THE TEMPERATURE E IGH NUMBER → E-8 I FLUX BASED RAYLEI	* E-7 IS: 347 BASED RAYLEIGH IS: 486.30E-03	7.42E-03 NUMBER IS :596.67E-03	
6	TEMPERATURE BASE % UNCERTAINTY IN FLUX BASED RAYLE	16.70E+00 D RAYLEIGH NUMBER THE TEMPERATURE E IGH NUMBER * E-8] FLUX BASED RAYLEI	* E-7 IS: 345 BASED RAYLEIGH IS: 484.82E-03	0.45E-03 NUMBER IS :599.56E-03	
7	TEMPERATURE BASE % UNCERTAINTY IN FLUX BASED RAYLE	17.61E+00 D RAYLEIGH NUMBER THE TEMPERATURE E IGH NUMBER * E-8 I FLUX BASED RAYLEI	* E-7 IS: 367 BASED RAYLEIGH IS: 496.47E-03	7.76E 303 NUMBER IS :568.68E-03	
8	TEMPERATURE BASE % UNCERTAINTY IN FLUX BASED RAYLE	17.22E+00 D RAYLEIGH NUMBER THE TEMPERATURE B IGH NUMBER * E-8 I FLUX BASED RAYLEI	* E-7 IS: 358 BASED RAYLEIGH IS: 495.81E-03	3.03E-03 NUMBER IS :581.69E-03	

10.81E-01 16.61E+00 14.23E+00 60.32E-02 TEMPERATURE BASED RAYLEIGH NUMBER * E-7 I5: 343.28E-03 2 % UNCERTAINTY IN THE TEMPERATURE BASED RAYLEIGH NUMBER IS: 602.77E-03 FLUX BASED RAYLEIGH NUMBER * E-8 IS: 488.34E-03 2 & UNCERTAINTY IN FLUX BASED RAYLEIGH NUMBER IS: 227.49E-04

REDUCED DATA FOR INPUT POWER 3.0 W BOTTOM BOUNDARY INSULATED

Nu

ZUNC IN Nu

THE RAW Emf DATA ARE FROM THE L'ILE: 08231310
THE POWER SETTING PER CHIP WAS: 3.0 WATTS

Tavg-Ts

CHIP

ONET(W)

1	29.78E-01 24.31E-02 TEMPERATURE BASED RAYLEIGH NUMBER * E-7 IS: 110.90E-02 Z UNCERTAINTY IN THE TEMPERATURE BASED RAYLEIGH NUMBER IS: 242.30E-03 FLUX BASED RAYLEIGH NUMBER * E-8 IS: 17.54E-02 Z UNCERIAINTY IN FLUX BASED RAYLEIGH NUMBER IS: 202.57E-04
2	29.77E-01 40.60E-00 16.28E-00 24.74E-02 TEMPERATURE BASED RAYLEIGH NUMBER * E-7 IS: 108.55E-02 % UNCERTAINTY IN THE TEMPERATURE BASED RAYLEIGH NUMBER IS: 246.54E-03 FLUX BASED RAYLEIGH NUMBER * E-8 IS: 176.18E-02 % UNCERTAINTY IN FLUX BASED RAYLEIGH NUMBER IS: 202.65E-04
3	29.72E-01 39.13E-00 16.84E-00 25.66E-02 TEMPERATURE BASED RAYLEIGH NUMBER * E-7 15: 102.84E-02 % UNCERTAINTY IN THE TEMPERATURE BASED RAYLEIGH NUMBER 15:255.82E-03 FLUX BASED RAYLEIGH HUMBER * E-8 IS: 173.21E-02 % UNCERTAINTY IN FLUX BASED RAYLEIGH NUMBER IS: 203.01E-04
4	23.42E-01 40.51E+00 16.12E+00 24.79E-02 TEMPERATURE BASED RAYLEIGH NUMBER * E-7 IS: 107.32E-02 % UNCERTAINTY IN THE TEMPERATURE BASED RAYLEIGH NUMBER IS: 247.08E-03 FLV. BASED RAYLEIGH NUMBER SE: 315: 173.38E-02 % UNCERTAINTY IN FLUX BASED RAYLEIGH NUMBER IS: 205.02E-04
5	29.55E-01 39.52E-00 16.59E-00 25.41E-02 TEMPERATURE BASED RAYLEIGH NUMBER * E-7 IS: 104.27E-02 2 UNCERTAINTY IN THE TEMPERATURE BASED RAYLEIGH NUMBER IS:253.28E-03 FLUX BASED RAYLEIGH HUMBER * E-8 IS: 1/2.94E-02 2 UNCERTAINTY IN FLUX BASED RAYLEIGH NUMBER IS: 204.15E-04
6	-23.44E-01 41.15E+00 15.99E+00 24.42E-02 TEMPERATURE BASED RAYLEIGH NUMBER * E-7 IS: 110.27E-02 2 UNCERTAINTY IN THE TEMPERATURE BASED RAYLEIGH NUMBER IS: :243.29E-03 FLUX BASED RAYLEIGH HUMBER * E-8 IS: 175.19E-02 204.93E-04
7	29.97E-01 41.77E+00 15.89E+00 24.05E-02 TEHPÉRATURE BASED RAYLEIGH NUMBER * E-7 IS: 112.63E-02 % UNCERTAINTY IN THE TEHPÉRATURE BASED RAYLEIGH NUMBER IS: 239.64E-03 FLUX BASED RAYLEIGH NUMBER $*$ E-8 IS: 178.94E-02 % UNCERTAINTY IN FLUX BASED RAYLEIGH NUMBER IS: 201.94E-04
8	22,95E-01 40,95E-00 16,25E-00 24,53E-02 TEMPÉRATURE BASED RAYLEIGH NUMBER * E-7 IS: 109.55E-02 2 UNCERTAINTY IN THE TEMPÉRATURE BASED RAYLEIGH NUMBER IS: 244.43E-03 FLUX BASED RAYLEIGH NUMBER * E-8 IS: 177.95E-02 2 UNCERTAINTY IN FLUX BASED RAYLEIGH NUMBER IS: 201.34E-04
9	29.72E-01 39.63E+00 16.64E+00 25.34E-02 TEHPERATURE BASED RAYLEIGH HUNBER * E-7 I5: 104.65E-02 TUNCERTAINTY IN THE TEMPERATURE BASED RAYLEIGH HUNBER IS: 252.60E-03 FLUX BASED RAYLEIGH HUNBER * E-8 I5: 174.11E-02 TUNCERTAINTY IN FLUX BASED RAYLEIGH MUNBER IS: 203.00E-04

TEMPERATURE DATA FOR INPUT POWER 0.1 W CHAMBER WIDTH = 30 mm

```
RESULTS ARE STORED IN FILE: 10161810
    EXPERIMENT CARRIED OUT AT
    AMBIENT TEMP (CELSIUS) OF:
                                  24.33
    BATH TEMP : 10 C-10 C
    TEMPERATURE READINGS IN DEGREES CELSIUS
         CENTER TOP RIGHT LEFT
12.806 12.761 12.736 12.771
                                         BOTIOM
                                                   BACK
CHIP NO1: 12.806 12.761
                                12.771 12.616
                                                  15.431
   POWER (WATIS): .0983
CHIP NO2: 12.954 12.894 12.591
                                12,861 12,816
                                                  15.438
    POWER (WATTS): .099
CHIP NO3: 13.099 12.956 00.000
                                12,986
                                         13,076
                                                   15.451
    POWER (WATTS): .0996
CHIP NO4: 12.764 12.731 12.536
                                12.574 12.484
                                                   15.441
    POHER (HATIS): .0990
CHIP NO5: 12.831 12.894 12.836
                                12.824
                                         12.801
                                                   15.446
   POHER (HATIS): .0993
CHIP NO6: 13.019 12.914 12.979
                                11.858
                                         12.746
                                                   15.448
   POWER (WATTS): .0995
CHIP NOT: 12.689 12.686 12.706
POWER (WATTS): .0992
                                                   15.445
                                12.684
                                         12.559
CHIP NO8: 13.039 12.941 12.966 00.000
                                        12,901
                                                   15.442
   POWER (WATTS): .0990
CHIP NO9: 13.256 13.114 12.834 13.144 13.144
                                                  15,445
   POWER (WATTS): .0992
   HEAT EXCHANGERS TEMPERATURES:
                                     RIGHT
                                             CENTER LEFT
        BOITOM:
                                            10.012 09.997
                                    09.967
                                    10.037
                                           00.000 10.042
        TOP:
   BACK PLANE TEMPERATURES :
    T(55): 12.656
   1(56):
          12.961
    1(57): 12,709
    T(74): 13.131
    T(75): 13.561
   T(76): 13.671
    I(77): 13.366
   SOURCE VOLTAGE: 1.225
   VOLTAGE TO THE HEATERS :
               .972
   CHIP #1:
   CHIP #2:
               1.027
    CHIP #3:
              1.022
               1.024
    CHIP #4:
                .368
    CHIP #5:
   CHIP #6:
               1.022
    CHIP #7:
               1.023
   CHIP #8:
              1.023
    CHIP #9:
               1.023
```

TEMPERATURE DATA FOR INPUT POWER 0.7 W CHAMBER WIDTH = 30 mm

```
RESULTS ARE STORED IN FILE: 10170950
    EXPERIMENT CARRIED OUT AT
    AMBIENT TEMP (CELSIUS) OF:
                                        24.78
    BATH TEMP : 10 C-10 C
    TEMPERATURE READINGS IN DEGREES CELSIUS
           CENTER
                     TOP
                             RIGHT
                                       LEFT
                                                 BOTTOM
                                                            BACK
CHIP NO1: 21.48
                    21.22
                                       21.31
                                                            24.28
                              21.08
                                                20.01
    POWER (WATTS): .708
CHIP NO2: 22.18 21.50
POWER (WATTS): .712
                              18.45
                                       21.41
                                                20.88
                                                            24.34
CHIP NO3: 22.65 21.48 00.00 POWER (WATTS): .719
                                       21.56
                                                21.98
                                                            24.44
CHIP NO4: 21.68 21.26
POWER (WATTS): .715
                             20.78
                                       21.12
                                                20.37
                                                            24.39
CHIP NO5: 21.93 21.19
POWER (WATTS): .718
                                                            24.42
                             21.53
                                       21.74
                                                21.48
CHIP NO6: 22.75 21.81 22.07
POWER (WATTS): .721
                                       20.73
                                                20.12
                                                            24.48
CHIP NO7: 21.14 20.83 2
POWER (WATTS): .719
                             21.34
                                       20.95
                                                19.34
                                                            24.44
CHIP NO8: 22.00 21.42 21.32
                                       00.00
                                                20.87
                                                            24.43
    POWER (WATTS): .718
CHIP NO9: 22.65 20.64 18.15
POWER (WATTS): .717
                                       22.02
                                                21.83
                                                            24.42
                       .717
                                                              LEFT
    HEAT EXCHANGERS TEMPERATURES:
                                           RIGHT
                                                    CENTER
                                                   10.017 09.972
          BOTTOM:
                                          09,922
          TOP:
                                          09.977
                                                   00.000 10.060
    BACK PLANE TEMPERATURES
    1(55): 15.191
    I(56):
             15,611
    T(57):
             14.265
    I(74):
             15,651
    T(75):
             16.079
    T(76):
             16.521
    T(77):
            15.350
    SOURCE VOLTAGE: 3,288
    VOLTAGE TO THE HEATERS :
    CHIP #1:
                 2.610
    CHIP #2:
                  2.756
                  2.743
    CHIP #3:
    CHIP #4:
                  2.747
    CHIP #5:
                  2.597
    CHIP #6:
                  2.741
    CHIP #7:
                  2.743
    CHIP #8:
                  2.744
    CHIP #9:
                  2.745
```

TEMPERATURE DATA FOR INPUT POWER 1.1 W CHAMBER WIDTH = 30 mm

	10171720		
EXPERIMENT CARRIED OUT AT AMBIENT TEMP (CELSIUS) OF: BATH TEMP : 10 C-10 C	25.94	16	
TEMPERATURE READINGS IN DEGREE CENTER TOP RIGHT CHIP NOT: 26.38 25.79 25.94 POHER (HATTS): 1.092		BOTTOM 24.21	BACK 29.857
CHIP NO2: 27.34 26.00 22.01 POWER (WATTS): 1.099	26.17	25.62	29.96
CHIP NO3: 27.67 25.73 00.00 POWER (WATTS): 1.1093	26.08	26.69	30.11
CHIP NO4: 26.74 26.07 25.51	26.00	24.85	30.02
CHIP NO5: 29.78 25.86 26.40	26.71	26.35	30.08
POWER (WATTS): 1.107 CHIP NOG: 27.51 25.54 26.74	25.65	24.17	30.16
POWER (WATTS): 1.113 CHIP_NO7: 25.80	25.63	22.98	30.10
POWER (WATTS): 1.109 CHIP NO8: 27.06 25.80 26.15	00.00	25.29	30.11
POWER (WATIS): 1.109 CHIP NO9: 27.79 24.71 21.36 POWER (WATIS): 1.110	26.94	26.60	30.11
HEAT EXCHANGERS TEMPERATURES:	09.9	HT CENTER 24 10.015	09.987
TOP:	10.0	10 00.000	10.068
	10.0	10 00.000	10.068
TOP: BACK PLANE TEMPERATURES: 1(55): 15.88 1(56): 17.48 1(57): 15.70 1(74): 17.57 1(75): 18.00 1(76): 18.49	10.0		10.068

TEMPERATURE DATA FOR INPUT POWER 1.5 W CHAMBER WIDTH = 30 mm

```
RESULTS ARE STORED IN FILE:
                                      10181020
    EXPERIMENT CARRIED OUT AT
     AMBIENT TEMP (CELSIUS) OF:
                                        23.94
    BATH TEMP :
                     10 C-10 C
     TEMPERATURE READINGS IN DEGREES CELSIUS
                                                 BOTTOM
           CENTER
                      TOP
                              RIGHT
                                       LEFT
                                                            BACK
CHIP NO1: 33.07
                    32.50
                              32.62
                                       32.72
                                                29.91
                                                         35.55
    POWER (WATTS): 1.484
CHIP NO2: 34.32 32.62 2
POWER (WATTS): 1.493
                                                         35.68
                              27.17
                                       32.75
                                                31.80
CHIP NO3: 34.63 32.10 00
POWER (WATTS): 1.5077
                                       32.62
                                                33.39
                                                         35.89
                            00.00
CHIP NO4: 33.56 32.40
POWER (WATTS): 1.501
                                                         35.79
                              31.90
                                       32.49
                                                30.83
CHIP NO5: 33.39 32.19
POWER (WATTS): 1.506
                                                32.64
                                                         35.87
                             32.67
                                       33.16
CHIP NO6: 34.02
POWER (WATTS):
                    31.20
                              33.07
                                       32.41
                                                29.59
                                                         35.97
                     1,513
CHIP NOT: 32.02
POWER (WATTS):
                    30.79
                                                27.98
                                                         35.89
                              32.47
                                       31.73
                     1,508
CHIP NO8: 33.89
                    32.28 32.71
                                       00.00
                                                31.39
                                                         35.89
    POWER (WATTS): 1.507
CHIP NO9: 34.69 31.22
                              26.04
                                       33.41
                                                33.00
                                                         35.88
    POWER (WATTS): 1.507
    HEAT EXCHANGERS TEMPERATURES:
                                           RIGHT
                                                    CENTER
                                                              LEFT
          BOTTOM:
                                          10.027
                                                   10.098
                                                            10.073
          TOP:
                                          10.108
                                                   00.000
                                                             10,126
    BACK PLANE TEMPERATURES
     T(55):
             19.59
     I(56):
             20.25
             17.80
     T(74):
             21.09
     T(75):
     T(76):
             21.47
     T(77):
             19.69
                                                     $
    SOURCE VOLTAGE: 4.767
    VOLTAGE TO THE HEATERS :
    CHIP #1:
                  3.787
    CHIP #2:
                  3.997
                  3.979
    CHIP #3:
    CHIP #4:
                  3.983
                  3.767
    CHIP #5:
                  3.975
    CHIP #6:
                  3.979
    CHIP #7:
    CHIP #8:
                  3.979
    CHIP #9:
                  3.979
```

FILE: 30MM10R

THESE RESULTS ARE NOW STURED ON DISK 'FASTSCAN

TEMPERATURE DATA FOR INPUT POWER 2.5 W CHAMBER WIDTH = 30 mm

```
RESULTS ARE STORED IN FILE: 10182338
    EXPERIMENT CARRIED OUT AT
    AMBIENT TEMP (CELSIUS) OF:
                                    23,17
    BATH TEMP :
                   10 C
    TEMPERATURE READINGS IN DEGREES CELSIUS
          CENTER
                    TOP
                          RIGHT
                                   LEFT
                                          ROTTOM
                                                   BACK
CHIP NO1: 42.47
                  41.80
                                   42.04
                                           37.20
                                                   49.73
                          41.39
    POWER (WATTS): 2.461
CHIP NO2: 44.31 40.93
                           41.68
                                   41.68
                                           40.14
                                                   49,93
                    2.475
    POWER (WATTS):
CHIP NO3: 44.77 41.10
                          00.00
                                   41.43
                                           42.66
                                                   50.28
    POWER (WATTS): 2.4985
CHIP NO4: 42.78 40.79
                                   41.00
                                           38.73
                                                   50.08
                          40.47
    POWER (WATTS):
                   2.485
CHIP NO5: 42.58 42.08
                          41.60
                                   42.36
                                           41.83
                                                   50.20
    POWER (WATTS): 2.494
CHIP NO6: 42.77 38.65 4
POWER (WATTS): 2.507
                          41.30
                                   41.37
                                           35.79
                                                   50.41
CHIP NO7: 40.63 39.59
                                   40.51
                          41.08
                                           34.17
                                                   50.25
                    2.497
    POWER (WATTS):
CHIP NO8: 42.02 39.95
                          40.79
                                   00.00
                                           37.88
                                                   50.27
                   2.498
    POWER (WATTS):
CHIP NO9: 42.77 37.10
                          41.32
                                   41.32
                                           40.60
                                                   50.24
    POWER (WATTS): 2,496
    HEAT EXCHANGERS TEMPERATURES:
                                      RIGHT
                                               CENTER
                                                        LEFT
         BOTTOM:
                                      10.020
                                              10.110
                                                       10.065
         TOP:
                                      09.748
                                              00,000
                                                       10.015
    BACK PLANE TEMPERATURES :
    T(55): 21.28
    T(56):
            22.30
    T(57):
            19,47
            23.34
    T(74):
    T(75):
            22.77
    1(76):
            23.81
                                                   t
            21.70
    SOURCE VOLTAGE: 6.142
    UNLIAGE IN THE HEATERS :
    CHIP #1:
                4.881
    CHIP #2:
                5.152
    CHIP #3:
                5.128
    CHIP #4:
                5.135
                4.859
    CHIP #5:
    CHIP #6:
                5.124
                5.129
    CHIP #7:
    CHIP #8:
                5.129
    CHIP #9:
                5.129
```

TEMPERATURE DATA FOR INPUT POWER 3.0 W CHAMBER WIDTH = 30 mm

```
RESULTS ARE STORED IN FILE:
                                   10232224
    EXPERIMENT CARRIED OUT AT
                                      22.83
    AMBIENT TEMP (CELSIUS) OF:
    BATH TEMP : 10 C
TEMPERATURE READINGS IN DEGREES CELSIUS
           CENTER
                     TOP
                            RIGHT
                                     LEFT
                                             BOTTOM
                                                       BACK
CHIP NO1: 50.66
                    49.62
                                     49.97
                            49.07
                                              43.61
                                                       57.87
    POWER (WATTS): 3.022
CHIP NO2: 52.71 47.
POWER (WATTS):
                  47.72
                            49.42
                                     49,42
                                              46.37
                                                       58.10
                       3.038
CHIP NO3: 52.51
                  48.65
                            00.00
                                     47.22
                                              49.87
                                                       58.53
    POWER (WAITS): 3.0672
CHIP NO4: 51.15 47.96
POWER (WATTS): 3.051
                            48.59
                                     48.79
                                              46.00
                                                       58.30
CHIP NO5: 50.48
                  48.36
                                     50.54
                                              48.61
                                                       58.47
                            49.36
    POWER (WATTS):
                     3.063
CHIP NO6: 51.67 42.15
POWER (WATIS): 3.079
                            48.38
                                     47.63
                                              46.09
                                                       58.70
CHIP NO7: 48.27
                  46.25
                            48.70
                                     48.07
                                              39.78
                                                       58.52
    POWER (WATTS):
                       3.066
                  45.58
CHIP NO8: 49.10
                            48.05
                                     00.00
                                              44.02
                                                       58.53
    POWER (WATTS): 3.067
CHIP NO9: 50.71
                  41.39
                            43.01
                                     43.01
                                              45.34
                                                       58.49
    POWER (WATTS): 3.064
    HEAT EXCHANGERS TEMPERATURES: RIGHT
                                              CENTER
                                                       LEFT
          BOTTOM:
                                     10.057
                                              10.166
                                                       10.176
          TOP:
                                     10.073
                                              00.000
                                                       10.163
    BACK PLANE TEMPERATURES
    1(55):
            24.75
    T(56):
             26.51
    I(57):
             22.64
    I(74):
             28.00
    T(75):
             26.95
    T(76):
             28.63
                                                     *
    T(77):
            25.41
    SOURCE VOLTAGE: 6.807
    VOLTAGE TO THE HEATERS:
    CHIP #1:
                 5.411
    CHIP #2:
                 5.712
    CHIP #3:
                 5.685
    CHIP #4:
                 5.692
    CHIP #5:
                 5.385
    CHIP #6:
                 5.680
    CHIP #7:
                 5.685
    CHIP #8:
                 5.685
    CHIP #9:
                 5,686
```

REDUCED DATA FOR INPUT POWER 0.1 W CHAMBER WIDTH = 30 mm

TH	1E	POL	IER	SE	H	INC	; P	FR	C	HIP	. NU	S:	ILE WAS	0.1	1016 MM	51810
CH:	IΡ	(ME	T (()	Τā	ıvg	T	s		N	lu l			Nu2	
1	AV	UX ERA NK	IGE	TE	MP	ERF	HU	RE	:	12.	861	t. 1 *	9 E-9	IS	10.85	.31
2	AV	UX ERA NK	AGE	TE	MP	ERI	TU	RE	:	12.	925	. 7	7 E-9	IS	10.66	
3	AV	UX ERA NK	1GE	TE	MP	ERF	HILL	RE	:	13.	144	.3 *	12 E-9	IS	9.98	.31
4	AV	UX ERA NK	GE	TE	MPI	ERF	UTF	RE	:	12.	734	1.4 *	E-9	IS	11.46	.31
	AV	UX ERF NK	IGE.	TE	MPI	ERF	ìΙU	RE	:	12.	934	* *	2 E-9	IS	10.68	.31
6	AV	UX ERF	1GE	1 E	MPI	ERF	aTU	RE	:	12.	788	*	1 E-9	IS	11.28	.31
7	AV	UX	BA:	SE D	RE	AYL ERC	EI	GH RE	: N	UMB	ER 782	*	0 E-9	IS	11.2B	.31
8	HV	UX ERA NK	IGE.	11	MPI.	-KF	3 I U	ΚŁ	:	13.	089	.5 *	8 E-9	IS	10.10	.31
9	AV	UX ERF	1GE	TE	MP	FRE	1111	RE	:	13.	202	*	E-9	15	9.75	.31

REDUCED DATA FOR INPUT POWER 0.7 W CHAMBER WIDTH = 30 mm

	Τŀ	IF I	POL	WEF	2 5	FT	TII	HG.	PF	R	CHI	IP.	WA!	S:	(1.7	H M MM		7095
CI	H)	[P	(BMC	11	H)		Tav	۱ā-	Ts			N	u 1			Nu	2	
	1	ΑV	ERI	AGE	. 1	EM	PE	RA:	I UF	₹E :	NUI 2	1.2	40 R 94	.87 • E	-9	IS	19.	12	2.41
	2	AV	ER	AGE	I	EM	PEI	RA'	TUF	RE:	иии 20),9	42 R 90	.23 * E	-9	IS	19.	76 2	2.42
;	3	ΑV	ER	AGE	. 1	EM	PEI	RA:	TUF	E:	NUN 22 . 0 7	2.1	38 R 85	. 48 * E	-9	IS	18.0	00 2	2.48
	4	AV	ERI	age	. 1	EM	PEI	RAI	LUE	E:	NUN 21 .07	1.2	41 R 73	.37 * E	-9	IS	19.3	36 2	2.44
!		F L I	FRE	₽GE	1	EM	PEI	RAI	TUR	E:	21	. 7	39 R + 83	.73 * E	-9	IS	18.5	59 2	2.46
(5	AVI	RF	age	. 1	EM	PEI	₹∩ Ι	UR	E:	NUI 21 .07	. 8	39 R - 78	.61 E	-9	IS	18.5	53 2	2.48
i		FLI AVI SII	F.R.	₽GE	. 1	EM	PEI	RAI	UR	Ε:	21	.0	42 R + 66	. 38 • E	-9	IS	19.8	3 3 2	. 45
1		FLU AVI SII	JX ER <i>f</i>	BA AGE	T	EM	PEF	RAI	UR	Ε:	21	.6	40 R + 85	. 07 • E	-9	IS	18.7	75 2	. 46
		FLU AVI	ERF	₽GE	. 1	EM	PEF	₹คา	UR	E:	21	. 2	41. R = 35	64 F.	-9	15	19.4	18	. 44

REDUCED DATA FOR INPUT POWER 1.1 W CHAMBER WIDTH = 30 mm

THE RAN EMF DATA ARE FROM THE FILE: 10171720
THE PONER SETTING PER CHIP WAS: 1.1 W
THE DISTANCE TO THE FRONT WALL WAS 30 MM

- CHIP ONET(N) Tavg-Is Nu1 Nu2
- 1 1.08 16.00 44.33 20.74 FLUX BASED RAYLEICH HUMBER * E-9 IS: 3.93 AVERAGE TEMPERATURE: 26.089 SINK TEMPERATURE: 10.085
- 2 1.09 15.48 46.12 21.58 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 3.94 AVERAGE TEMPERATURE: 25.565 SINK TEMPERATURE: 10.085
- 3 1.10 16.83 42.84 20.04 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 4.03 AVERAGE IEHPERATURE: 26.917 SINK TEMPERATURE: 10.085
- 4 1.09 16.05 44.67 20.90 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 3.98 AVERAGE TEMPERATURE: 26.136 SINK TEMPERATURE: 10.085
- 5 1.10 17.57 40.98 19.17 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 4.06 AVERAGE TEMPERATURE: 27.657 . STHK TEMPERATURE: 10.085
- 6 1.10 16.42 44.03 20.60 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 4.03 AVERAGE IEMPERATURE: 26.509 SINK IEMPERATURE: 10.085
- 7 1.10 15.60 46.18 21.60; FLUX BASED RAYLEIGH NUMBER * E-9 IS: 3.98 AVERAGE TEMPERATURE: 25.688 SINK TEMPERATURE: 10.085
- 8 1.10 16.43 43.88 20.53 FLUX BASED RAYLEIGH NUMBER ◆ E-9 IS: 4.02 AVERAGE TEMPERATURE: 26.519 SINK TEMPERATURE: 10.085
- 9 1.10 15.63 46.12 21.58 FLUX BASED RAYLEIGH NUMBER * E-9 I5: 3.98 AVERAGE TEMPERATURE: 25.717 SINK TEMPERATURE: 10.085

REDUCED DATA FOR INPUT POWER 1.5 W CHAMBER WIDTH = 30 mm

T T T	HE POI	4 Emf HER SE STANCE	DATA TTING TO T	ARE F PER HE FR	ROM T CHIP ONT F	HE FIL WAS: MALL WA	E: 1.5 S 30	1021 H MM	113
CH	IP (ONET CH	l) Ta	vg-Ts		Null		Nu2	
1	AVER	1.52 BASED AGE TE TEMPE	MPERA	TURE:	32.5	44.65 R * E- 69	9 IS:	0.89	.94
2	SINK	AGE TE TEMPE	MPERA RATUR	TURE: E: 10	31.9				
3	AVER	1.54 BASED AGE TE TEMPE	MPERA	ITURE:	34.2	42.22 R * E- 52	9 IS:	9.75 6	. 15
4	AVER	1.54 BASED AGE TE TEMFE	MPERA	TURE:	32.4	45.37 R * E- 150	9 IS:	1.23 6	.00
5	FLUX AVERI	1.54 BASED AGE TE TEMPE	RAYL MPERA RATUR	23.39 EIGH TURE: E: 10	NUMBE 33.5 .180	43.35 R * E- 74	9 IS:	0.28 6	.09
6	AVER	1.55 BASED AGE TE TEMPE	MPERA	TURE:	-32.7	45.06 R * E- 88	9 IS:	1.08 6	.07
7	AVER	1.54 BASED AGE TE TEMPE	MPERA	TURE:	31.8	46.86 R * E- 37	9 IS:	1.92 [†] 5	. 99
8	FLUX AVER	1.54 BASED GE TE TEMPE	RAYL MPERA	EIGH TURE:	NUMBE 32.4	45.54 R * E- 82	9 IS:	1.30 6	.03
9	AVER	1.54 BASED PGE TE TEMPE	MPERA	TURE:	30.7	49.26 R * E- 82	9 IS:	3.05 5	.92

REDUCED DATA FOR INPUT POWER 2.5 W CHAMBER WIDTH = 30 mm

THE RAN Emf DATA ARE FROM THE FILE: 10182338 THE POWER SETTING PER CHIP WAS: 2.5 W THE DISTANCE TO THE FRONT WALL WAS 30 MM

CHIP ONET(W) Tavg-Ts Nu1 Nu2

- 2.44 31.61 51.08 23.90 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 10.54 AVERAGE TEMPERATURE: 41,698 SINK TEMPERATURE: 10.087
- 2.45 30.24 53.65 25.10 FLUX BASED RAYLEJGH NUMBER * E-9 IS: 10.44 AVERAGE TEMPERATURE: 40.331 SINK TEMPERATURE: 10.087
- 2.48 33.03 49.69 23.25 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 10.86 AVERAGE TEMPERATURE: 43.113 SINK TEMPERATURE: 10.087
- 2.46 31.27 52.14 24.39 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 10.60 AVERAGE TEMPERATURE: 41.356 SINK TEMPERATURE: 10.087
- 2.47 32.19 50.86 23.79 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 10.74 AVERAGE TEMPERATURE: 42.277 SINK TEMPERATURE: 10.087
- 2.49 31.14 52.84 24.72 FLUX BASED RAYLEJGH NUMBER * E-9 IS: 10.68 AVERAGE TEMPERATURE: 41.225 SINK TEMPERATURE: 10,087
- 30.10 54.39 2.48 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 10.52 AVERAGE TEMPERATURE: 40.189 SINK TEMPERATURE: 10.087
- 2.48 30.94 52.97 24.78 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 10.62 AVERAGE TEMPERATURE: 41.023 SINK TEMPERATURE: 10.087
- 2.48 28.94 56.51 26.44 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 10.39 AVERAGE TEMPERATURE: 39,028 SINK TEMPERATURE: 10.087

REDUCED DATA FOR INPUT POWER 3.0 W CHAMBER WIDTH = 30 mm

TH	IF POI	WER !	SEIT	ING	PER	CHIE	WAS	FILE:	.0 1	4	1913	10
CH!	[P (ONET	(11)	Ta	vg-1	s	Nu	1		Nu2		
1	AVER	AGE	TEMPE	ERA	TURE	9 NUME : 48. 0.154	440	36 E-9	15:	4.0	3 13.7	3
2	AVER	AGE	TEMPE	ERA	TURE	0 NUME : 46. 0.154	657	14 E-9	IS:	5.3	3 13.5	6
3	AVER	AGE	TEMP	ERA	TURE	0 NUME : 48. 0.154	959	50 E-9	15:	4.1	0 14.0	3
4	AVER	AGE	TEMPE	ERA	TURE	3 NUME : 48. 0.154	185	27 E-9	2 IS:	4.4	6 13.8	5
5	FLUX AVER	BASI AGE	ED RA TEMPE	YLI RA	E I GH TURE	2 NUME : 48. 0.154	ER *	66 E-9	2 IS:	4.1	7 13.9	8
6	AVER	AGE	TEMPE	RA	TURE	0 NUME : 46. 0.154	755	74 E-9	15:	5.6	13.7	6
7	AVER	AGE	TEMPE	ERA	TURE	9 NUME : 46. 0.154	642	71 E-9	15:	5.6	0 [*] 13.6	9
8	AVER	AGE	TEMPE	ERA	TURE	2 NUME : 46. 0.154	771	55 E-9	IS:	5.5	2 13.7	2
9	AVER	BASE AGE	ED RA	YL!	I I GH TURE	7 NUME : 43. 0.154	ER *	88 E-9	15:	B.0	1	3

TEMPERATURE DATA FOR INPUT POWER 0.1 W CHAMBER WIDTH = 9 mm

```
RESULTS ARE STORED IN FILE: 11050029
    EXPERIMENT CARRIED OUT AT
    AMBIENT TEMP (CELSIUS) OF:
                                    22.78
    BATH TEMP :
                   10 C
    TEMPERATURE READINGS IN DEGREES CELSIUS
          CENTER
                    TOP
                          RIGHT
                                 LEFT BOTTOM
                                                   BACK
CHIP NO1: 14.34
                  14.25
                          14.16
                                   14.24
                                           14.08
                                                   14.40
                      .097
    POWER (WATTS):
CHIP NO2: 14.48
                 14.33
                           14.32
                                   14.32
                                           14.22
                                                   14.54
    POWER (WATTS):
                      .098
CHIP NO3: 14.58
                 14.53
                           14.49
                                           14.54
                                                   14.64
                                   14.48
    POWER (WATIS):
                       .0989
                 14.25
CHIP NO4: 14.39
                           14.10
                                   14.12
                                           14.02
                                                   14.45
    POWER (WATTS):
                      .099
CHIP NOS: 14.43
                  15.89
                          14.33
                                   14.37
                                           14.26
                                                   14.49
    POWER (WATTS):
                      .039
CHIP NO6: 14.65
                  14.37
                                   14.24
                                           14.58
                                                   14.71
                           00.00
    POWER (WATTS):
                      .099
CHIP NO7: 14.13
                 14.14
                           14.19
                                   14.17
                                           14.08
                                                   14.19
    POWER (WATTS):
                      .099
CHIP NO8: 14.59
                  14.41
                           14.42
                                   00.00
                                           14.24
                                                   14.65
    POWER (WATTS):
                       .099
CHIP NO9: 14.71
                 14.28
                           16.01
                                   16.01
                                           14.45
                                                   14.77
    POWER (WATTS):
                     .099
    HEAT EXCHANGERS TEMPERATURES: RIGHT
                                           CENTER
                                                    LEFT
         BOITOM:
                                   09.914
                                           09.967
                                                   09,965
         TOP:
                                   10.011
                                           00.000
                                                   10.392
    BACK PLANE TEMPERATURES :
    T(55): 12.97
    1(56):
            13.12
    T(74):
            13.52
    T(75):
            13.83
    T(76):
            13.99
                                                 *
            13.25
    1(77):
    SOURCE VOLTAGE: 1,219
    VOLTAGE TO THE HEATERS :
                .967
    CHIP #1:
    CHIP #2:
                1.021
    CHIP #3:
                1.016
    CHIP #4:
                1.017
    CHIP #5:
                 .962
    CHIP #6:
                1.015
    CHIP #7:
                1.015
    CHIP #8:
                1.015
```

CHIP #9:

1.016

TEMPERATURE DATA FOR INPUT POWER 0.7 W CHAMBER WIDTH = 9 mm

```
RESULIS ARE STURED IN FILE: 11062057
    EXPERIMENT CARRIED OUT AT
    AMBIENT TEMP (CELSIUS) OF:
                                     20.61
    BATH TEMP :
                    10 C
    TEMPERATURE READINGS IN DEGREES CELSIUS
           CENTER
                    TOP
                           RIGHT
                                    LEFT
                                           BOTTOM
                                                     BACK
CHIP NO1:
          23.48
                  23.75
                   23.27
                           22.85
                                    23.21
                                            21.49
                                                     23,88
    POWER (WATTS):
CHIP NO2: 24.85
                           23.74
                                    23.74
                                            23.07
                                                     25,26
    POWER (WATTS):
CHIP NO3: 24.78
                  24.57
                           24.32
                                    23.70
                                            24.51
                                                     25.19
                       .7050
    POWER (WATTS):
                   22.97
CHIP NO4: 23.92
                           22.82
                                    22.78
                                            21.97
                                                     24.32
    POWER (WATTS):
                       .703
CHIP NOS:
                   23.82
          24.77
                           24.12
                                    24,42
                                            23,69
                                                     25.17
    POWER (WATTS):
                       .705
CHIP NO6:
                           00.00
          25.92
                   23.76
                                    23.15
                                            25.35
                                                     26.33
    POWER (WATTS):
                       .709
                   22.57
CHIP NO7:
          23.12
                           23.13
                                    22.84
                                            21.02
                                                     23.53
    POHER (WATTS):
                       .707
                  23.90
CHIP NO8: 24.84
                                    00.00
                                            22.83
                                                     25.25
                           23.94
    POWER (WATTS):
                     .707
CHIP NO9: 25.78 22.75
                           19.26
                                    23.34
                                            24.30
                                                     26.19
                       .706
    POWER (WATTS):
    HEAT EXCHANGERS TEMPERATURES: RIGHT
                                            CENTER
                                                     LEFT
         BOTTOM:
                                    09.972
                                            10.070
                                                     10.088
         TOP:
                                    10.047
                                            00.000
                                                    10.137
    BACK PLANE TEMPERATURES
    T(55):
            15.17
    I(56):
             15.45
    T(74):
             15.92
    1(75):
             15,99
    T(76):
            16.29
                                               1
    T(77):
            15.68
    SOURCE VOLTAGE:
                      3,259
    VOLTAGE TO THE HEATERS :
    CHIP #1:
                2.587
    CHIP #2:
                 2.731
    CHIP #3:
                 2.720
    CHIP #4:
                 2.722
    CHIP #5:
                 2.575
    CHIP #6:
                2.717 2.718
    CHIP #7:
                 2.718
    CHIP #8:
    CHIP #9:
                2,720
```

TEMPERATURE DATA FOR INPUT POWER 1.1 W CHAMBER WIDTH = 9 mm

```
RESULTS ARE STORED IN FILE: 11022255
    EXPERIMENT CARRIED DUT AT
     AMBIENT TEMP (CELSIUS) OF:
                                        21.11
     BATH TEMP : 10 C
TEMPERATURE READINGS IN DEGREES CELSIUS
           CENTER
                            RIGHT
                                       LEFT
                                             BOTTOM
                      TOP
                                                         BACK
CHIP NO1: 28.92 28.61
POWER (WATTS): 1.093
                              28,26
                                       28.57
                                                25.77
                                                         29.87
CHIP NO2: 31.27 29.86 POWER (WATTS): 1.100
                              29.60
                                       29.60
                                                28.52
                                                         29.97
CHIP NO3: 30.49 30.42 3
POHER (WATTS): 1.1071
                             30.02
                                       28.65
                                                30.37
                                                         30.08
CHIP NO4: 29.63 28.45 28.11
                                                26.78
                                                         30.04
                                       27.89
    POWER (WATTS): 1.104
CHIP NOS: 31.16 29.79 30.20
POWER (WATTS): 1.107
                                                29.54
                                       30.63
                                                         30.08
CHIP NO6: 31.91 28.89 (
POWER (WATTS): 1.114
                             00.00
                                       28.72
                                                31.17
                                                         30.18
CHIP NO7: 28.48 27.51
                              28.46
                                       28.34
                                                25.07
                                                         30, 15
    POWER (WATTS): 1.112
CHIP NO8: 31.20 30.08 3 POWER (WATTS): 1.111
                             30.00
                                       00.00
                                                28.01
                                                         30.14
CHIP NO9: 32.68 28.26
                             31.03
                                       31.03
                                                30.57
                                                         30.11
    POWER (WATTS):
                      1.110
    HEAT EXCHANGERS TEMPERATURES: RIGHT
                                                CENTER
                                                         LEFT
          BOTTOM:
                                       09.839
                                                10.128 10.241
          TOP:
                                       09.863
                                                00.000 09.952
    BACK PLANE TEMPERATURES :
    T(55): 17.38
     T(56):
              17.58
    T(74):
             18.00
     T(75):
             18.02
     T(76):
             18.41
     1(77):
             17.63
    SOURCE VOLTAGE: 4.086
    VOLTAGE TO THE HEATERS :
                  3.244
    CHIP #1:
     CHIP #2:
                  3.425
    CHIP #3:
                  3.411
     CHIP #4:
                  3,413
     CHIP #5:
                  3,229
     CHIP #6:
                  3.406
    CHIP #7:
                  3.407
     CHIP #8:
                  3,408
     CHIP #9:
                  3,409
```

TEMPERATURE DATA FOR INPUT POWER 1.5 W CHAMBER WIDTH = 9 mm

```
RESULIS ARE STORED IN FILE: 11091225
    EXPERIMENT CARRIED DUT AT
    AMBIENT TEMP (CELSIUS) OF:
                                          21.83
    BATH TEMP : 10 C
     TEMPERATURE READINGS IN DEGREES CELSIUS
            CENTER
                       TOP
                              RIGHT
                                        LEFT
                                                 BOTTOM
                                                            BACK
CHIP NO1: 36.71 36.38 3 POWER (WATTS): 1.489 CHIP NO2: 38.97 36.79
                                         36.25
                                                   32.76
                                                            37.56
                               35.78
                               37.06
                                         37.06
                                                   35.88
                                                            39.83
     POWER (WATTS): 1.497
CHIP NO3: 38.33 37.92 37.67
POHER (HATIS): 1.5093
CHIP NO4: 37.06 35.37 35.16
POWER (HATIS): 1.504
                                         34.98
                                                  37.83
                                                            39,20
                                         34.59
                                                   33.41
                                                            37.92
CHIP NOS: 38.29 36.57 37.19
POWER (WATTS): 1.508
CHIP NO6: 39.40 35.38 00.00
                                         37.75
                                                  36.20
                                                            39.16
                                         34.97
                                                   38.23
                                                            40.27
    POWER (WATTS): 1.516
CHIP NO7: 34.94 33.67 35.04
POWER (WATTS): 1.512
                                                   30.18
                                         34.46
                                                            35.81
CHIP NO8: 38.18 35.83 36.98
POWER (WATTS): 1.512
                                         00.00
                                                   34.50
                                                            39.05
CHIP NO9: 39.71 34.80 28.60
                                         36.52
                                                            40.58
                                                   36.89
                        1.511
    POWER (WATTS):
    HEAT EXCHANGERS TEMPERATURES: RIGHT
                                                   CENTER
                                                            LEFT
                                         09.828 09.977
           BOTTOM:
                                                            10.040
           TOP:
                                         10.007
                                                            10.295
                                                  00.000
    BACK PLANE TEMPERATURES
    T(55):
             20.82
     1(56):
              21.73
     T(74):
              22.48
              22.33
     T(75):
     T(76):
              22.64
                                                     t
     T(77):
              21.31
    SOURCE VOLTAGE: 4.771
    VOLTAGE TO THE HEATERS :
    CHIP #1:
                   3.789
    CHIP #2:
                   4.000
    CHIP #3:
                   3.983
    CHIP #4:
                   3.987
    CHIP #5:
                   3.772
    CHIP #6:
                   3.979
    CHIP #7:
                   3.981
    CHIP #8:
                   3.982
    CHIP #9:
                   3.983
```

TEMPERATURE DATA FOR INPUT POWER 2.5 W CHAMBER WIDTH = 9 mm

```
RESULTS ARE STORED IN FILE: 11082020
    EXPERIMENT CARRIED OUT AT
    AMBIENT TEMP (CELSIUS) OF:
                                      21.28
    BATH TEMP : 10 C
    TEMPERATURE READINGS IN DEGREES CELSIUS
           CENTER
                    TOP
                           RIGHT
                                    LEFT BOTTOM
                                                      BACK
CHIP NO1: 46.62 45.93 4
POWER (WATTS): 2.504
                            45.41
                                    46.08
                                             40.22
                                                      48.05
CHIP NO2: 50.04 46.15
                            47.23
                                                      51.48
                                    47.23
                                             43.85
    POWER (WATTS): 2.520
CHIP NO3: 48.91 48.75 48.04
POWER (WATTS): 2.5388
                                    45.63
                                             48.30
                                                      50.37
CHIP NO4: 47.00 43.52 44.22
                                    42.84
                                             41.35
                                                      48.45
    POWER (WATTS): 2.531
CHIP NO5: 48.77 46.61 47.23
                                    48.29
                                             45.89
                                                      50.23
    POHER (WATTS): 2.538
CHIP NO6: 49.99 44.34 00.00
-POWER (WATTS): 2.552
                                    44.08
                                             48.13
                                                      51.45
CHIP NO7: 43.36 41.13 43.65
POWER (WATTS): 2.544
                                    42.69
                                             35.63
                                                     44.82
CHIP NO8: 48.86 45.42 47.09
POWER (WATTS): 2.544
CHIP NO9: 49.89 42.54 34.29
                                                     50.32
                                     00.00
                                             43.17
                                     45.52
                                             45.93
                                                     51.35
    POWER (WATTS): 2,541
    HEAT EXCHANGERS TEMPERATURES: RIGHT
                                             CENTER
                                                       1 FF f
          BOTTOM:
                                     09.859
                                              10.037
                                                      10,110
          TOP:
                                     09.803
                                             00.000 10.073
    BACK PLANE TEMPERATURES :
    1(55): 22.95
            24.01
    T(56):
            24.80
    T(74):
    T(75): 24.59
    1(76):
           24.97
                                                $
    I(77): 23.67
    SOURCE VOLTAGE: 6,193
    VOLTAGE TO THE HEATERS :
                4,921
    CHIP #1:
                 5.193
    CHIP #2:
    CHIP #3:
                5.172
    CHIP #4:
                5.176
    CHIP #5:
                4.897
    CHIP #6:
                5.165
    CHIP #7:
                5.169
    CHIP #8:
                5.169
    CHIP #9:
                5.171
```

TEMPERATURE DATA FOR INPUT POWER 3.0 W CHAMBER WIDTH = 9 mm

```
RESULTS ARE STORED IN FILE: 11072058
    EXPERIMENT CARRIED OUT AT
    AMBIENT TEMP (CELSIUS) OF:
                                     21.00
    BATH TEMP :
                    10 C
    TEMPERATURE READINGS IN DEGREES CELSIUS
           CENTER
                     TOP
                           RIGHT
                                   LEFT
                                           BOTTOM
                                                     BACK
CHIP NOT: 55.97
                  54.46
                           55.08
                                    55.59
                                            45.61
                                                     57.66
    POWER (WATTS): 2.938
CHIP NO2: 61.12
                   57.34
                           58.19
                                    58.19
                                            54.57
                                                     62.82
    POWER (WATTS): 2.957
CHIP NO3: 58.47
                 58.54
                           57.89
                                    55.35
                                            58.30
                                                     60.18
    POWER (WATTS): 2.9774
CHIP NO4:
          57.35 53.88
                           54.52
                                    54.33
                                            49.46
                                                     59.05
    POWER (WATTS): 2.969
          58.98 57.68
CHIP NOS:
                           58.44
                                    59.12
                                            56.79
                                                     60.69
    POWER (WATIS): 2.978
CHIP NO6: 61.17 55.49
                           00.00
                                    55.89
                                            59.33
                                                     62.89
    POWER (WATTS): 2.993
          52.97 51.59
CHIP NOT:
                           53.54
                                    53.26
                                            43.41
                                                     54.68
    POWER (WATTS):
                      2.984
CHIP NO8: 60.57 57.20
                           59.10
                                    00.00
                                            54.97
                                                     62.28
POWER (WATTS): 2.985
CHIP NU9: 60.45 53.52
                           46.33
                                    56.95
                                            56.66
                                                     62.17
                    2,984
    POWER (WATTS):
    HEAT EXCHANGERS TEMPERATURES: RIGHT
                                            CENTER
                                                     LEFT
                                                     10.176
         BOTTOM:
                                    09,783
                                            10,022
         TOP:
                                    09.816
                                            00.000
                                                    10.063
    BACK PLANE TEMPERATURES
    T(55):
            32.35
    T(56):
             34.45
    T(74):
            35.59
    T(75):
             35.08
    T(76):
            35.20
                                               4
    T(77):
            33.52
    SOURCE VOLTAGE: 6.715
    VOLTAGE TO THE HEATERS : CHIP #1: 5.339
    CHIP #2:
                 5.633
    CHIP #3:
                 5.611
    CHIP #4:
                5.615
5.314
    CHIP #5:
    CHIP #6:
                 5,603
    CHIP #7:
                5.608
    CHIP #8:
                 5.607
    CHIP #9:
                5.608
```

REDUCED DATA FOR INPUT POWER 0.1 W CHAMBER WIDTH = 9 mm

1	THE THE	RA PO DI	H E HER STA	mf SE NCE	DAT	A F NG TE	RE PEI	FR R C FRO	OM HIP NT	THE WAL	F S: L	ILE: U WAS	1.1 9 M	1105 H IM	0029
Cŀ	HIP		ONE	TO	1)	Tav	·g-	Ts		N	lu I			Nu2	
	ρ	LUX IVER INK	AGE	TE	MPE	RAI	UR	E:	14.	242	* I	9 E-9	:21	7.11	.30
4	A	LUX IVER INK	AGE	TE	MPE	RAT	UR	Ε:	14.	221	* 1	8 E-9	ıs:	7.19	,31
	A	L UX VER INK	AGE	TE	MPE	RAI	UR	Ε:	14.	525	* (3 E-9	IS:	6.75	.31
ı	A	LUX VER INK	AGE	TE	MPE	RAI	UR	Ε:	14.	208	. 5 * (4 E-9	IS:	7.27	.31
į	· A	L UX VER INK	AGE	TE	MPE	RAT	UR	Ε:	14.	497	* {	2-9	15:	6.80	.31
6	Α	LUX VER INK	AGE	TE	MPE	RAI	URI	Ε:	14.	473	. 7 * {	0 E - 9	IS:	6.88	.31
7	A	LUX VER INK	AGE	TE	MPE	RAT	UR	Ε:	14.	153	. 8 * - [5 - 9	IS:	7.42	.31
8	F	LUX VER INK	BA AGE	TE	MPE	RAT	URI	Ε:	14.	471	• 6 * [7 E-9	IS:	6.86	.31
9	A	LUX VERI	AGE	TE	MPE	RAT	URI	Ε:	14.	660	. 0 i	D - 9	IS:	6.55	.31

REDUCED DATA FOR INPUT POWER 0.7 W CHAMBER WIDTH = 9 mm

	HE RAI	4 Emf [HER SET	DATA F	RE FE PER (ROM THE	HE FIL	E: 1 0.7 W IS 9 MM	106205
		ONE T (W.						
1	AVER	.68 BASED AGE TEN TEMPER	1PERA1	URE:	23.1	34.38 R * E- 74	9 15:	08 2.41
2	AVER	.69 BASED AGE TEN TEMPER	1PERA1	URE:	23.2	34.42 R * E- 51	16. 9 IS:	2.43
3	AVER	.69 BASED AGE TEN TEMPER	1PERA 1	URE:	24.4	31.75 R * E- 56	9 IS:	86 2.48
	AVER	.69 BASED AGE TEN TEMPER	1PERA 1	URE:	23.2	34.63 R * E 19	16. 9 IS:	20 2.44
5	AVER	.69 BASED AGE TEN TEMPER	1PERA1	URE:	24.4	31.75 R * E- 51	9 IS:	86 2.48
6	AVER	.70 BASED AGE TEN TEMPER	1PERA I	URE:	24.7	31.20 R * E- 94	9 IS:	
7	AVER	.70 BASED AGE TEN TEMPER	1PERAT	URE:	22.93	35.62 R * E- 33	16. 9 IS:	96 2.44
8	AVER	.70 BASED AGE TEN TEMPER	1PERAT	URE:	24.3	32.16 R * E- 13	9 IS:	04 2.48
9	FLUX AVER	.69 BASED GE TEN TEMPER	RAYLE IPERAT	JGH N URE:	1UMRE1 23.21	₹ ¥ E-	16. 9 IS:	21 2.45

REDUCED DATA FOR INPUT POWER 1.1 W CHAMBER WIDTH = 9 mm

11	IE IE IE	RA PO DI	INE INE	R	m f	E	AC T T	TA IN O	G T I	PE HE	R	FR	MO! IH: IMI	P F	HE WAS	F 5:	ILI NA:	E: 1	. 1 9	H MM	110	122	255
CH)	ĮΡ		10	ΙE	T (Н)	Ī	a١	ıą.	. 1	s			Ni	11				N	12		
	FL	UX	A	BA:	SE	D E I	Ri 1Pi	A Y E R	LE	JU	E H	:	MUI	BE • 3	38 R -	F	7 E-9	9	15	18	. 19	4.	02
2	FL	UX	E A	BA:	SE T	D EI	RI	AY ER	LE Al	IUF	SE	. N	UH	BE.	38 R 25	•	9 E-9	9	15	17.	. 87	4.	07
	FL	UX	A	A:	SE T	D E	Ri	a Y E R	LE Al	IUF	RE	: :	UM	BE . 8	36 R 9								14
4	A١	ΈR	A(ξE	T	E١	1P1	ER	A1	UF	ŖΕ	:	UM 28 19	. 4	39. R 1	. 0	6 E - S	9	IS	18	. 28	4.1	07
5	A۷	'ER	A(ŀΕ	T	Εř	1PI	ER	Αl	UF	₹E	:	UM 30 19:	.5	35 . R : 38	2	6 E - S	9	IS	16.	. 49	4.	17
6	FL	UX ER	E A	A:	SE T	D E t	R/	a Y E R	LE Al	UF	H;	. N	UMI	BE . 4	35 . R +	- 1	5 E - 9	9	IS	16.	.68	4.	19
7	FL	UX ER NK	A	A:	SE T	D E.t	R/ 1Pl	a Y E R	LE A I	UF	E H	: :	UH 28 19	BE . O	40 . R = 76	2	3 E-5	9	IS	18.	82	4.1	08
8	A۷	ER	A(Œ	Ĩ	E١	1PI	ER	Αl	UF	ŖΕ	:	UM 30 19:	.3	35 . R = 21	, 7 • 1	6 E - 9	9	IS	16.	. 73	4.	18
9	FL	UX ÆR	AC	BA:	SE T	D El	Ri 1PI	a y E R	LE	UF	H RE	: N	UM	BE 3	37 R =	4	3 E - 9	9	IS	17.	.51	4.	13

REDUCED DATA FOR INPUT POWER 1.5 W CHAMBER WIDTH = 9 mm

11091225 .5 W 9 MH
Nu2
17.45 IS: 5.96
17.59 IS: 6.00
16.90 IS: 6.13
17.96 IS: 5.99
16.70 IS: 6.15
16.92 IS: 6.17
18 5 .93 IS: 5.95
17.01 IS: 6.13
18.07 IS: 6.02

REDUCED DATA FOR INPUT POWER 2.5 W CHAMBER WIDTH = 9 mm

11082020

THE RAW Emf DATA ARE FROM THE FILE:
THE POWER SETTING PER CHIP WAS: 2.5 W
THE DISTANCE TO THE FRONT WALL WAS 9 MM CHIP ONEI(W) Tavo-Is Nu t 2.47 35.42 46.27 21.65 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 11.15 AVERAGE TEMPERATURE: 45.692 SINK TEMPERATURE: 10.271 2.49 35.23 46.82 21.90 FLUX BASED RAYLFIGH NUMBER * E-9 IS: 11.20 AVERAGE TEMPERATURE: 45.503 SINK TEMPERATURE: 10.271 2.50 37.64 44.23 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 11.58 AVERAGE TEMPERATURE: 47.908 SINK TEMPERATURE: 10.271 2.50 34.33 48.22 22.56 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 11.14 AVERAGE TEMPERATURE: 44.605 SINK TEMPERATURE: 10.271 2.50 37.68 44.17 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 11.58 AVERAGE TEMPERATURE: 47,946 SINK TEMPERATURE: 10.271 2.52 37.02 45.18 21.14 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 11.56 AVERAGE TEMPERATURE: 47.287 SINK TEMPERATURE: 10.271 2.51 32.27 51.53 24.11 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 10.96

2.51 37.08 44.97 21.04 FLUX BASED RAYLEIGH NUMBER * F-9 IS: 11.53 AVERAGE TEMPERATURE: 47.355 SINK TEMPFRATURE: 10,271

AVERAGE TEMPERATURE: 42,536 SINK TEMPERATURE: 10.271

2.51 33.79 49.19 FLUX BASED RAYLEIGH NUMBER * E-9 IS: 11.12 AVERAGE TEMPERATURE: 44.057 SINK TEMPERATURE: 10,271

REDUCED DATA FOR INPUT POWER 3.0 W CHAMBER WIDTH = 9 mm

THE F	OWER SETT	IA ARE FROM ING PER CHI O THE FRONT	P WAS:	: 11072058 3.0 W 9 MM
CHIP	QNET(W)	Tavg-Is	Nu1	Nu2
FLL	JX BASED RI ERAGE TEMP	44.40 AYLEIGH NUM ERATURE: 54 TURE: 10.36	BER * E-9 .762	20.42 IS: 14.41
AVE	JX BASED RI ERAGE TEMP	46.34 AYLEIGH NUM ERATURE: 56 TURE: 10.36	BER * E-9 .697	19.72 IS: 14.79
AVE	IX BASED R	47.28 AYLEIGH NUM ERATURE: 57 TURE: 10.36	BER * E-9 .639	19.47 IS: 15.04
FLL	JX BASED RI ERAGE TEMP	44.68 AYLEIGH NUM ERATURE: 55 TURE: 10.36	BER * E-9 .040	20.51 IS: 14.61
AVE	JX BASED RI ERAGE TEMPI	48.33 AYLEIGH NUM ERATURE: 58 TURE: 10.36	BER * E-9 .691	19.06 IS: 15.20
AVE	IX BASED RERECTEMP	48.31 AYLEIGH NUM ERATURE: 58 TURE: 10.36	BER * E-9 .676	19.17 IS: 15.28
FLL	JX BASED RI RAGE TEMPI	42.01 AYLEIGH NUM ERATURE: 52 TURE: 10.36	BER * E-9 .372	21.89 IS: 14.29
AVE	RAGE TEMPI	48.82 AYLEIGH NUM ERATURE: 59 IURE: 10.36	.183	18.92 IS: 15.31
AVE	IX BASED RE	44.89 AYLEIGH NUM ERATURE: 55 TURE: 10.36	BER * E-9 .253	20.52 IS: 14.71

APPENDIX D

SOFTWARE LISTING

```
PROGRAM CalcDiel
 20
21
23
30
31
                          ! EDITED BY LT E. TORRES. FROM ORIGINALS OF
! PAMUK [REF.12] AND BENEDICT [REF. 13]
                         ! THIS PROGRAM ANALYSES THE DATA READ FROM +
! A DATA FILE DESIGNATED BY THE OPERATOR.IT +
! REDUCES THE DATA TO CALCULATIONS OF NET +
! POMER. PAYLEIGH NUMBER AND MUSELT NUMBER. +
50
                         VARIABLES USED ARE:
1 EMF: VOLTAGE FROM THE THERMOCOUPLES.
2 POWER : POWER DISSIPATED BY THE MEATERS.
3 T(1) : TEMPERATURE CONVERTED FROM THERMOCOUPLES.
 96
                                                                  PLES VOLTAGE.
                                TAVG: 13 THE AVERAGE TEMPERATURE OF THE CHIP. IT IS OBTAINED MULTIPLYING THE TEMPERATURE FOUND IN EACH FACE BY THE AREA AND DIVIDING BY THE TO-
                        BY THE AREA AND DIVIDING BY THE 10-
TAL AREA.

TAL AREA.

TAL AREA.

THE STATE OF THE FC-75.

DIET: SLECTRIC POWER HINUS COMPUCTION LOSSES.

THE UPPER AND LOBER HEAT-EXCHANGERS.

HOUSE TO SERVICE OF THE STATE OF T
                          ! OTHER VARIABLES ARE SELF EXPLANATORIES.
                         COM /Co/ D(7)
                          DIM Emi (76), Power (3), T(76), Tavq (9), Ts(3)
                          DIM Tt:lm(9).Onet(9).H(9).k(9).Rho(9).Cp(9)
                          DIM N(9), Nu(9), Ra(9), Delt(9), Alta(9), Pr(9)
                          DIM Gr(9), Beta(9), Dpow(9), Dts(9), Rp(8)
                         200
210
211
220
250
270
280
                         PEAD DIAL
                          READ Rp(+)
                         PRINTER IS 701
                          BEEP
                          BEEP
 500
  300
                          INPUT "ENTER THE NAME OF THE FILE CONTAINING DATA". 01dfile$
                          PRINT USING "10X,""THE RAW Emf DATA ARE FROM THE FILE: "".10A":01dfiles
                           INPUT "ENTER THE POWER SETTING ". Powers
```

```
PRINT USING "9X."" THE POWER SETTING PER CHIP WAS: "", 10A": Powers
340
341
      PRINT USING "TOX." THE DISTANCE TO THE FRONT WALL WAS 9 MM """
344
350
370
      PRINT
380
       BEEP
390
       BEEP
       ASSIGN #File TO Oldfile$
400
401
       ENTER @File:Emf(+)
410
420
       ! CONVERT Emf TO DEGREES CELSIUS ..
430
431
43
440
      FOR I=0 TO 60
450
      Sum=0
460
       FOR J=0 TO 7
470
       Sum=Sum+D(J)*Emf(I)'J
480
       NEXT J
490
      T(I)=Sum
500
      NEXT I
502
       FOR I=71 TO 76
       Sum=1)
504
       FOR J=0 TO 7
506
       Sum*Sum*D(J) *Emf(I) 'J
508
       NEXT J
509
      T(I)=Sum
510
511
513
520
       ! CONVERT Emf TO POHER *
521
522
530
       .1=1
       Volt=Emf(61)
       FOR I=62 TO 70
Power(J)=Emf(I)=(Vol+-Emf(I))/Rp(I-62)
       NEXT I
       144444444
      ! AREA OF THE BLOCK FACES .
612
520
630
       Acen=1.92E-4
       Alei=1.44F-4
       Arigs1.44E-4
640
       Atop=4.3E-9
       Abot=4.8E-5
                                                                 4
670
       Ato+=5.76E-4
580
630
631
       !CALCULATE THE AVERAGE TEMPERATURES OF THE BLOCK FACES + !IF A THERMOCCUPLE IS FOUND OPENED.IT SHOULD BE TAKEN OFF.+
700
701
       710
       Tavg(1)=(T(0)+Acen+T(1)+Atop+T(2)+Arig+T(3)+Alet+T(4)+Abot)/Atot
Tavg(2)=(T(6)+Acen+T(7)+Atop+T(8)+Arig+T(9)+Alet+T(10)+Abot)/Atot
```

```
740
750
      Tavg(4)=(T(18)*Acen+T(19)*Atop+T(20)*Arig+T(21)*Alef+T(22)*Abot)/Atot
      760
770
780
790
       Tavg(9)=(T(48)+Acen+T(49)+Atop+T(50)+Arig+T(51)+Alef+T(52)+Abot)/Atot
800
      ! RESISTANCE OF PLEXIGLASS. FOUND WITH A CONDUCTIVITY OF * ! 0.195 H/m.K AND A LENGTH OF 19.5 MM.
852
853
860
      Rc=520.83
890
      ! CHIP BACK SURFACE TEMPERATURES .
       900
       Ts(1)=T(5)
      Ts(2)=T(11)
Ts(3)=T(17)
      Ts(4)=T(23)
Ts(5)=T(29)
940
950
      Ts(6)=T(35)
       Ts(7)=T(41)
960
970
      Ts(8)=T(47)
980
      Ts(9)=T(53)
      Issum=1)
      FOR J=1 TO 3
      Issum=Issum+Ts(J)
1020
      NEXT J
1040
      Tsavg=Tssum/3
1041
1060
       ! CONDUCTION LOSS CALCULATION. *
1061
1062
      010ss3=(T(17)-T(75))/Rc
      010ss5=(T(29)-T(55))/Rc
      01oss7=(T(41)-T(54))/Rc
1090
      Oloss=(Qloss3+0loss5+0loss7)/3
1120
       ! AVERAGE SINK TEMPERATURE CALCULATION *
       Isiak=(T(57)+T(58)+T(59)+T(60)+T(71)+T(72)1/6
       THO CHARACTERISTIC LENGTHS.WILL BE USED TOGALCULATE HUSSELT HUMBERS :
LI BASED IN THE VERTICAL DIMENSION OF THE CHIEF (24,MM)
AND L2 BASED IN THE SUMNITION OF THE AREASOLVIDED BY THE PERIMETER.
1154
      L1=2.40E-2
L2=(2.+16.+24./60.)+2.*(8.+6./28.)+8.424./54.)+.001
 1161
       ! TO PRINT THE OUTPUT HEADINGS. *
 1174
                                                                 Nu2 "",10A"
 1180 PRINT USING "9X," "CHIP ONET(W) Tavg-Ts Nul
 1200 PRINT
 1210
```

```
! CALCULATION OF NET POWER, No AND Ra. .
1220
1230
1231
     FOR J=1 TO 9
1250
1260
     ! CALCULATION OF Onet
1270
     Onet(J)=Power(J)-Oloss
1300
       CALCULATION OF Tfilm
1310
     If Ilm(J) = (Tavg(J) + Isink)/2
1340
     ! CALCULATION OF A DELTA TEMPERATURE
1350
     Delt(J)=Tava(J)-Tsink
      ! CALCULATION OF CONVECTION COEFFICIENT
1380
1390
     H(J)=Onet(J)/(Atot*Delt(J))
1410
1420
      ! CALCULATION OF FC-75 THERMAL CONDUCTIVITY.
1430 K(J)=(.65-7.89474E-4+Tfilm(J))/10
1440
1450
      ! CALCULATION OF FC-75 DENSITY
     Rho(J)=(1.825-.00246*Tfilm(J))*1000
1460
1470
     ! CALCULATION OF FC-75 SPECIFIC HEAT
1480
1490
     Cp(J)=(.241111+3.7037E-4+Tf:lm(J))+4180
1510
      ! CALCULATION OF FC-75 VISCOSITY
     N(J)=1.4074-2.964E-2*ffilm(J)+3.8018E-4*ffilm(J)*2-2.7308E-6+f+ilm(J)*3+8.
1520 N(J)=1.4074-.
1679E-9+Tfilm(J)^4
1530
     N(J)=N(J)+1.E-6
1540
1550
      ! CALCULATION OF THE COEFFICIENT OF THERMAL
1551
      ! EXPANSION [BETA]
1560 Beta(J)=,00246/(1.825-,00246*Tfilm(J))
1570
1580
      ! CALCULATION OF ALPHA
1590
     Aifa(J)=K(J)/(Rho(J)*Cp(J))
1600
1610 ! CALCULATION OF PRANDTL NUMBER.
1620 Pr(J)=N(J)/Alfa(J)
1630
1640
      ! CALCULATION OF NUSSELT NUMBERS
1650 Nu1(J)=H(J)+L1/K(J)
      Hu2(J)=H(J)+L2/K(J)
1670
1710
       ! CALCULATION OF GRASHOF NUMBER.
      Gr(J)=9.81*Beta(J)*(L1'3)*Del+(J)/N(J)'2
1720
1740
1750
      ! CALCULATION OF RAYLEIGH NUMBER.
1760
      Ra(J)=Gr(J)+Pr(J)+1.E-7
1780
1794
       ! CALCULATION OF FLUX BASED RAYLEIGH NUMBER
1810
      Raf(J)=((9.81*Beta(J)*L1*4*Onet(J))/(K(J)*N(J)*Al+a(J)*Ato+))*1.E-9
1830
1870
       PRINT USING "10X.D.1X.5(5X.DD.DD.)"; J.Onet(J), Delt(J), Nu1(J), Nu2(J)
1880
1890
      PRINT USING "12%.""FLUX BASED RAYLEIGH NUMBER - E-9 IS: "".DDD.DD":Raf(J)
BRINT USIN: "12%.""AVERAGE TEMPERATURE:".DDD.DDD":Taink
BRINT USIN: "ENTRY TEMPERATURE:".DDD.DDD":Taink
1930
1342
```

1960 NEXT J 1970 ASSIGN €File TO > 1980 END

```
1.0
        ! PROGRAM FASTSCAN +
       PROGRAM TO SCAN THE THREE UPPERMOST THERMOCOUPLES.
! IT SCANS 3 CHANNELS FOR TEMPERATURE VARIATION MEASUREMENTS.
30
40
41
        ! CHANNELS ARE 13,31 AND 49
50
        60
        Ipass=599
        Pass=1)
        N=0
        DIM T1(599).V1(2).Y1(599)
81
        DIM 12(599), V2(2), Y2(599)
DIM 13(599), V3(2), Y3(599)
82
90
        CLEAR 709
        CLEAR 72
        1 . . . . . . . . . . .
        ! THE THREE FILE NAMES THAT ARE REQUIRED FOLLOWING ! ARE TO STORE THE READINGS FROM THREE THERMOCOUPLES.
102
103
104
        ......
106
        BEEP
        PRINTER IS 701
108
        BEEP
        HRUT "ENTER THE FIRST FILE NAME: ".Mewfile.'S
IMPUT "ENTER THE SECOND FILE NAME: ".Mewfile.'S
IMPUT "EITER THE THAD FILE NAME: ".Mewfile.'S
IMPUT "EITER THE THAD FILE NAME: ".Newfile.'S
IMPUT "ENTER THE VOLTHETER READING: ".V$
PRINT USING "ISX." RESULTS ARE STORED ON DISK "FASTSCAN" ".10A"
109
110
        PRINT
114
116
        PRINT USING "25X, ""FILE: "", 10A": Newfile1S
        PRINT
118
        PRINT USING "25X, ""FILE: "". 10A": Newfile23
119
        PRINT
120
        PRINT USING "25X.""FILE: "".10A":Newfile3$
        PRIMIT
        WAIT 1
124
        BEEP
125
        OUTPUT 709: "AE!"
        WAIT 2
130
        BEEP
140
        OUTPUT 722: "T4 F1 R1 P0 Z0 1STI 501 1STN"
141
143
144
        ! LOOP NUMBER ONE
145
        146
        ! START SCANNING CHANNEL # 13 +
147
        OUTPUT 709: "AF13 AL13"
160
        QUITPUT 709: "AS"
        BEEP
170
        Timedatel * TIMEDATE
180
       FOR Jj=0 TO Ipass
OUTPUT 722:"T3"
ENTER 722:V1(*)
200
210
220
250
        T1(Pass)=V1(1)
        Pass=Pass+1
251
        N=N+1
260
261
        NEXT Jr
        Timedate2=TIMEDATE
263
        Dutbutime2: Amedate2-Timedate1
```

```
Pass=0
        1 LOOP NUMBER TWO
        ! START SCANNING CHANNEL 31
       OUTPUT 709: "AF31 AL31"
        DUTPUT 709: "AS"
       FOR Jj=0 TO lpass
OUTPUT 722:"T3"
ENTER 722:V2(+)
         2(Pass)=V211)
       Pass=Pass+;
NEXT J:
       OUTPUT 722: "AC31"
       Pass=0
       ! LOOF NUMBER THREE +
       ! START SCANNING CHANNEL 49 .
       OUTPUT 709: "AF49 AL49"
       DUTPUT 709: "AS"
       BEEP
       FOR J<sub>J</sub>=0 TO Ipass
OUTPUT 722: T3"
ENTER 722:V3(+)
        T34Pass)=V3(1)
       Pasa=Pass+1
207
208
309
310
       NEXT JJ
       1 END LOOPS
       PRINT USING "15%.""THE TOTAL TIME ELAPSED | SECONDS : "".2%, (DDD, DD) ": fotal
t mel
       PRINT USING "15%." THE TOTAL NUMBER OF SCANS : "".2%. DDDD.D.2% ":N
14
       PAINT USING "15%." THE VOLTMETER READING : "". 104.": 175
115
       PRINTER IS 1
I TRANSFER FIRST SCAN DATA
       TRANSFERING THE SCAN DATA FROM CHANNEL 13
TO THE FILE. THIS FILE WILL BE USED. WITH
THE PROGRAM "PLOT". TO MAKE A PLOT OF TEM-
       PERATURE VS TIME.
       CREATE BDAT Newfile13.20
ASSIGN #File TO Newfile13
       OUTPUT *File: T1(+)
       FOR I:=0 TO Ipass
       T1([1]=.10086091+25727.9+11([1]-767345.8+11([1])-2+79002556+11([1])-3
```

```
340
     NEXT II
341
     ! TRANSFER SECOND SCAN DATA +
342
      344
      !TRANSFERING DATA FROM CHANNEL 31+
345
346
      ITO THE FILE
347
349
      | **************
      CREATE BDAT Newfile23,20
350
351
      ASSIGN @File TO Newfile2$
OUTPUT @File:T2(+)
FOR I:=0 TO Ipass
352
353
      T2(I1)=,10086091+25727.9+12(I1)-767345.8+T2(I1) 2+78002556+T2(I1) 3 .
354
355
357
358
      NEXT II
      ! TRANSFER THIRD SCAN DATA
359
360
      ! TRANSFERING DATA FROM CHANNEL 31 +
361
      ! TO THE FILE.
362
363
      CREATE BDAT Newfile35.20
ASSIGN @File TO Newfile35
OUTPUT @File:T3(+)
FOR I:=0 TO Ipass
364
365
366
367
368
      T3(I1)*.10086091*25727.9*T3(I1)-767345.8*T3(I1)*2*78002556*T3(I1)*3
369
      NEXT II
390
      STOP
      END
400
```

5

```
! FILE NAME: PLOT
20
50
      ! THIS FROGRAM PLOTS THE DATA ACQUIRED BY
50
      ! PROGRAM "FASTSCAN".
30
       PRINTER IS 705
90
       BEEP
       Xmin=0
       Xmax = 200
120
       BEEP
       INPUT "ENTER MINIMUM AND MAXIMUM Y-VALUES". Ymin. Ymax
       BEEP
140
       Xstep=20
       BEEP
160
       Ystep=.2
130
        BEEP
       PRINT "IN:SP1:IP 2000,2000.8000.7000:"
190
       PRINT "SC 0.100.0.100;TL 2.0;"
200
       5fx=100/(Xmax-Xmin)
220
230
       Sfy=100/(Ymax-Ymin)
PRINT "PU 0.0 PD"
       FOR Xa=Xmin TO Xmax STEP Xstep
X=(Xa-Xmin)*Sfx
PRINT "PA":X.".0: XT:"
240
250
260
270
280
290
       PRINT "PA 100.0:PU:"
PRINT "PU PA U.O PD"
300
       FOR Ya=Ymin TO Ymax STEP Ystep
        Y=(Ya-Ymin)+Sfy
       PRINT "PA C,":Y, "YI"
       PRINT "PA 0.100 TL 0 2"
FOR Xa=Xmin TO Xmax STEP Xstep
340
360
        X=1Xa-Xmin)*Sfx
        PRINT "PA"; X. ". 100; XT"
       NEXT Xa
390
        PRINT "PA 100,100 PU PA 100,0 PD"
       FOR Ya=Ymin TO Ymax STEP Ystep
400
        Y=(Ya-Ymin1+Sfy
420
       PRINT "PD PA 100.".Y."YT"
       NEXT Ya
PRINT "PA 100.100 PU"
PRINT "PA 0.-2 SR 1.5.2"
FOR Xa=(min TG Xmax STEP Xstep
430
440
450
460
470
        X=(Xa-Xmin)*5rx
480
       PRINT "PA":X.".0:"
PRINT "CP -2,-1;LB":Xa:""
490
        NEXT Ya
        PRINT "PU PA 0.0"
       FOR Ya=Ymin TO Ymax STEP Ystep
       IF ABS(Ya)<1.E-5 THEN Ya=0
Y=(Ya-Ymin) +Sfy
540
        PRINT "PA 0.":Y.""
PRINT "CP -5.-.25;LB";Ya;""
560
        NEXT Ya
        BEEP
        IF Idl=0 THEN
```

```
520
         Xlabel3="Time (sec)"
630
         BEEP
640
         Ylabels="Temperature (C)"
550
         PRINT "SR 1.5.2:PU PA 50.-10 CP":-LEN(Xiabel$1/2:"0:LB":Xlabel$:""
660
         PRINT "PA -11,50 CP 0,";-LEN(Ylabel$)/2*5/6;"DI 0.1:LB":Ylabel$:""
670
        END IF
PRINT "CP 0.0"
630
        BEEP
700
         INPUT "ENTER THE NAME OF THE DATA FILE".D files
710
720
         ASSIGN @File TO D_file$
        BEEP
730
         Md=0
740
         BEEP
750
760
        Npairs=600
BEEP
770
        PRINTER IS 1
230
         Sym=1
        PRINTER IS 705
790
80ŏ
        PRINT "PU DI"
810
        IF Sym=1 THEN PRINT "SM."
IF Sym=2 THEN PRINT "SM+"
820
830
         IF Sym=3 THEN PRINT "SHo"
        IF Md>1 THEN
840
850
        FOR I=1 TO (Md-1)
360
        ENTER @File:Xa.Ya
370
        NEXT I
        END IF
890
        FOR Xa=0 TO 199 STEP .33333333
900
        ENTER @File:Ya
910
        Ya=.10086091+25727.9+Ya-767345.8+Ya-2+78002556+Ya-3
920
930
        X=(Xa-Xmin)*5fx
        Y= (Ya-Ymin)+Sfy
        IF Sym23 THEN PRINT "SM"
IF Sym24 THEN PRINT "SR 1.4.2.4"
PRINT "PA" X.Y."PD"
IF Sym23 THEN PRINT "SR 1.2.1.5"
940
950
960
970
        IF Sym=8 THEN PRINT "UC2.4.99.0.-8.-4.9.0.9.4.0.:"
IF Sym=5 THEN PRINT "UC3.0.39.-3.-6.-3.6.3.6.3.-6:
IF Sym=6 THEN PRINT "UC0.5.3.99.3.-8.-6.0.3.8!"
IF Sym=7 THEN PRINT "UC0.-5.3.99.-3.8.6.0.-3.-9:"
NEXT Xa
980
990
1000
1010
1020
        PRINT "PU"
1030
        BEEP
1040
        ASSIGN File 10 *
1050
        FND
```

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